0 n electronic shells surrounding charged insulated m etallic clusters

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Abstract

We determ ine the wavefunctions of electrons bound to a positively charged m esoscopic m etallic cluster covered by an insulating surface layer. The radius of them etal core and the thickness of the insulating surface layer are of the order of a couple of angstrom. We study in particular the electrom agnetic decay of externally located electrons into unoccupied internally located states which exhibits a resonance behaviour. This resonance structure has the consequence that the lifetime of the \m esoscopic atom s" may vary by up to 6 orders of magnitude depending on the values of the parameters (from sec to years).

1 Introduction

C lusters consisting of som e 10² to 10⁵ atom s, which can be produced for instance in the course of the condensation of vapour, have attracted great interest during the last 20 years. These "m esoscopic" clusters were found to exhibit classical as well as quantum m echanical features. In the special case of m etallic clusters [1], the conduction electrons, which m ove in the average potential produced by the positively charged ions, exhibit shell e ects. As a consequence, the binding energy of the cluster becom es a function of the num ber of free electrons (and thus also of the num ber of ions). In turn, this in plies m easurable variations of the form ation probability of a cluster as a function of its m ass in a therm al vapour-gas equilibrium.

O ther interesting types of mesoscopic systems are the so-called "fullerenes" which represent a crystal of atom s covering a closed, usually spherical surface [2]. A number of review articles exist on this exciting new eld of physics (see for instance Ref. [3] and Ref. [4] and books mentioned at the end of Ref. [1] and Ref. [2]).

In the present paper, we consider a mesoscopic system which consists of a spherical metallic core of radius R_2 carrying Z positive charges and surrounded by an insulating layer of external radius R_1 (see Fig. 1). We determ ine analytically the bound states of a single electron in the potential V (r) which is produced by the positive surface charge density of the metallic core and the insulating dielectric surface layer. As in the case of an ordinary atom, these

single electron wave functions describe also approximately the case that several electrons are bound in this potential. For Z bound electrons, the system has total charge 0. Because of the obvious similarity of this system with an atom or ion, we refer to it as a "m esoscopic atom " or "m esoscopic ion".

As one can sum ise, there are two di erent types of bound electronic states: electrons localized in the metallic core inside of the insulating layer (region II, Fig. 1) and electrons localized in the vacuum outside of the insulating layer (region 0, Fig. 1). The bound states localized outside are rem iniscent of the bound states of an electron in the C oulom b potential of the atom ic nucleus. W e are mainly interested in these externally localized electronic states ("class 1-states") and their decay into lower-lying bound states predom inantly localized within the metallic core ("class 2-states").

The paper is organized as follows:

In Sec. 2, we form ulate the single-particle H am iltonian and determ ine the eigenfunctions and eigenenergies of bound electrons. In doing so, we take into account the polarization of the insulating surface layer which is produced by the uniform positive charge distribution on the surface S_2 of the m etal, but we neglect the additional polarization elects produced by the externally localized electrons.

In Sec. 3 we determ ine these additional polarization e ects within the classical M axwellian electrodynamics. They lead to an additional potential acting on the electrons which is of importance close to the surface S_1 of the insulator. So far, we have not yet studied the electron of this additional potential on the externally localized electrons.

The Sec. 4 is dedicated to a presentation of the results. In Subsec. 4.1, we describe the procedure which we used in order to obtain the eigenvalues and eigenfunctions and we present typical examples of spectra and wavefunctions. In Subsec. 4.2, we discuss the electrom agnetic decay of a predom inantly externally localized bound electron into a lower-lying internally localized state. We show that the transition rate and the corresponding life-time m ay vary by several orders of m agnitude depending on the parameters of the system.

In general, the transition is hindered by the small overlap between externally and internally localized states ("class 1-states" and "class 2-states") if the insulating surface layer is su ciently thick. In particular, we discuss the special role in this decay of "class 3-states" which exhibit non-negligible amplitudes both in the external region 0 and the internal region II.

Finally, in Sec. 5, we sum marize the results and discuss som e related open questions.

2 Theory

In the single-particle H am iltonian for an electron bound to a positively charged and insulated m etallic core (M = m ass of the electron)

$$\hat{H} = \hat{T} + \hat{\Psi} = \frac{h^2}{2M} + V (r);$$
 (1)

the potential V (r) contains the interaction of the electron with the positive surplus charge $Z e_0$ ($e_0 = elementary$ charge) and with the ionic background ("jellium") of the metal. Furtherm ore, it contains the electron of the insulating surface layer. The radius R_2 of the metal and the thickness ($R_1 = R_2$) of the surface layer are assumed to be of the order of 5 to 20 A (1 A = 10⁻¹⁰ m) and the number Z of positive charges of the metal is considered to be 1 to 5. For these dimensions of the system we may expect that, on the one hand, the dynamics of the

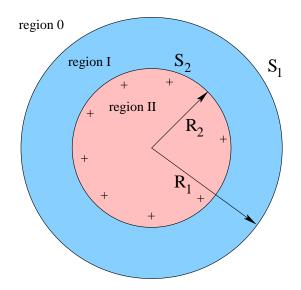


Figure 1: Schem atic view of the charged m etallic cluster (radius R_2 , surface S_2) covered by an insulating layer (outer radius R_1 , surface S_1). States of bound electrons predom inantly localized in the surrounding vacuum ($R > R_1$, region 0) are called "class 1-states" in distinction from states localized in the m etallic core ("class 2-states").

electron is fully quantum -m echanical and, on the other hand, we may use macroscopic concepts in formulating the potential V (r), at least as a rst approximation. So we assume that the positive surplus charge is uniform by distributed over the surface S_2 of the metal

$$_{2}(\mathbf{r}) = {}_{S_{2}} \qquad (\mathbf{r} {}_{2}\mathbb{R} = \frac{Z e_{0}}{4 R_{2}^{2}} \quad (\mathbf{r} {}_{R_{2}}):$$
 (2)

The C oulom b potential produced by this simple charge distribution acting upon an electron (charge φ) is given by

$$e_{0}^{2} d^{3}r^{0} \frac{2(r^{0})}{jr} = \frac{Z e_{0}^{2}}{R_{2}} (R_{2} r) \frac{Z e_{0}^{2}}{r} (r R_{2}); \qquad (3)$$

where $_0(x)$ is the Heaviside function

 $\int_{0}^{0} (x) = \begin{pmatrix} 1 & \text{for } x > 0 \\ 0 & \text{for } x < 0 \end{pmatrix} :$

Inside of the m etal, the conduction electrons feel not only the constant potential produced by the positive surface charge but also the attractive interaction with the ionic background which we represent by a constant negative potential V_{Π}^0 ($V_{\Pi}^0 > 0$).

On the other hand, the average energy gap above the Ferm i level in the insulator m ay act upon the electron like a repulsive barrier of a height $B_0 > 0$.

Last not least, there are polarization e ects produced by the positive surplus charge and also by the charge distribution $_{\rm e}$ (r) of the externally (i.e. predom inantly in region 0) localized electrons. The polarization e ects are investigated in Sec. 3 on the basis of M axwell's equations for the electric eld E and for the displacement eld D in the presence of hom ogeneous dielectric m edia. In the case that we only take into account the polarization e ects produced by the

positive surplus charge (2), the following modi cations of the Coulomb potential (3) are to be considered: W ithin region I, i.e. within the insulating layer, the Coulomb potential $Z \notin = r$ is to be replaced by

$$\frac{Z e_0^2}{r} ! \qquad \frac{Z e_0^2}{r} I'' \qquad \frac{Z e_0^2}{R_1} I''$$

and within region II, i.e. within the metallic core, the constant potential $Z \notin = R_2$ is to be supplanted by

$$\frac{Z e_0^2}{R_2} ! \frac{Z e_0^2}{R_2 "_{I}} \frac{Z e_0^2}{R_1 "_{I}} = \frac{Z e_0^2}{R_2} + Z e_0^2 \frac{1}{R_2} \frac{1}{R_1} \frac{"_{I}}{R_1} "_{I} :$$

W ithin region 0, i.e. in the vacuum surrounding the insulating layer, the value $Z \notin = r$ of the C oulom b potential (3) is unchanged.

One should note that the potential in region I assumes the value $Z \notin = R_1$ at the outer surface $r = R_1$ of the insulating layer.

Let us denote the sum of the constant parts of the potentials in region I and II by

$$B \coloneqq B_0 \quad \frac{Z e_0^2}{\mathbf{"}_{\mathrm{I}} R_1} (\mathbf{"}_{\mathrm{I}} \quad 1)$$
(4)

and

$$V_{II} \coloneqq V_{II}^{0} = Z \notin_{0}^{2} \frac{1}{R_{2}} - \frac{1}{R_{1}} - \frac{"_{I}}{"_{I}} = \frac{1}{T}$$
(5)

If Z is equal to 1 or 2 and the dielectric constant " $_{\rm I}$ exceeds 1 only slightly, and if the radii are in the range of values treated in Sec. 4, the 2nd term s on the right-hand sides of Eqs. (4) and (5) are much smaller than the 1st term s. So far, it is only these cases which we treated num erically.

A ltogether, the potential V (r) felt by the electron has the form

$$V(\mathbf{r}) = V_{II} + \frac{Z e_0^2}{R_2} |_{0}(R_2 - \mathbf{r}) + B - \frac{Z e_0^2}{\mathbf{r}_{I}\mathbf{r}} |_{0}(R_1 - \mathbf{r}) |_{0}(\mathbf{r} - R_2) - \frac{Z e_0^2}{\mathbf{r}} |_{0}(\mathbf{r} - R_1) : (6)$$

The constants V_{II} , "I and B₀ are empirical parameters. The potential V (r) is shown in Fig. 2 for a speci c choice of the parameters.

The eigenfunctions (r; #; ') of the Schrödinger equation

$$\frac{h^2}{2M} + V(r) = E$$
(7)

separate

$$(r; \#; ') = R (r) Y_{lm} (\#; ') = \frac{u(r)}{r} Y_{lm} (\#; ')$$
(8)

and the radial functions R (r) and u (r) have to satisfy the di erential equations

$$\frac{h^2}{2M} - \frac{d^2}{dr^2} + \frac{2}{r}\frac{d}{dr} - \frac{l(l+1)}{r^2} R + V (r)R = ER ; \qquad (9)$$

$$\frac{h^2}{2M} \quad \frac{d^2}{dr^2} \quad \frac{l(l+1)}{r^2} \quad u+V \ (r)u = E u \ ; \tag{10}$$

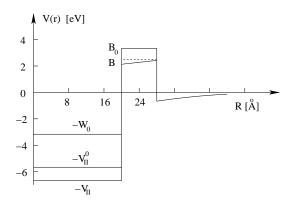


Figure 2: Sem i-quantitative picture of the potential V (r) for the following choice of parameters: $R_2 = 20 \text{ A}$; $R_1 = 30 \text{ A}$; Z = 1; $W_0 = 33 \text{ eV}$; $V_{II} = 63 \text{ eV}$; B = 3 eV; $"_I = 3$; $Z e_0^2 = ("_I \quad \underline{R}) = 0.24 \text{ eV}$; $Z e_0^2 = ("_I \quad \underline{R}) = 0.16 \text{ eV}$; $Z e_0^2 = R_1 = 0.48 \text{ eV}$:

respectively.

For $r < R_2$ (region II), the potential V (r) is constant and thus the Eq. (9) represents the di erential equation for "spherical Bessel functions". Of the 2 linearly independent solutions, only the regular one, j_1 , qualities as a physical solution. Up to a normalization factor which will be determined later on, the radial function R (r) in region II is simply given by

$$R_{II}(r) = j_{I}(I_{II}r);$$
 (11)

where $_{II}$ is defined by

$$_{\Pi} = \stackrel{V_{\Pi}}{\overset{U}{t}} \frac{\frac{Z e_{0}^{2}}{2M}}{h^{2}} + V_{\Pi} \qquad \stackrel{I}{\xrightarrow{}} E j$$
(12)

and $j_1(x)$ is the spherical Bessel function of the 1st kind (see Chapt. 9 of Ref. [5]). As bound states have an energy between the well depth $(V_{II} + Z e_0^2 = R_2)$ and 0, the parameter $_{II}$ is assured to be real.

 $\frac{\text{For } R_2 < r < R_1 \text{ (region I)}}{\text{to the sim pler situation when the r-dependent term } Ze_0^2 = ("_1r) \text{ is negligible in comparison to the constant B in the entire region I. This is so, if the inequality}$

$$\frac{Z e_0^2}{"_{IR_2}} << B$$
 (13)

holds. For the case shown in Fig. 2, the condition is fullled. Generally speaking, the barrier heights B_0 range from 2 to 5 eV, and the dielectric constant " $_{\rm I}$ m ay have values between slightly m ore than 1 up to m ore than 100 (E xam ples: " $_{\rm I}$ (caoutchouc) = 4; " $_{\rm I}$ (T iO₂-crystal) = 115).

Let us now investigate the case that the potential (6) can be approximated by

V (r)
$$V_{II} + \frac{Z e_0^2}{R_2}^{\#} {}_{0} (R_2 r) + B_0 (R_1 r)_0 (r R_2) \frac{Z e_0^2}{r} {}_{0} (r R_1) :$$
 (14)

The radial Schrödinger equation (9) in region I then assumes again the form of Bessel's dierential equation. But as the energy E is lower than the barrier height B, the solution in region I is given by a linear combination of two independent "m odi ed spherical Bessel functions" (see Chapt. 10.2 of Ref. [5]).

We choose the pair $(i)^{1}j_{1}(iy); = i^{1}h_{1}^{(1)}(iy)^{\circ}$, where $j_{1}(iy)$ and $h_{1}^{(1)}(iy)$ are the spherical Bessel-function and spherical Hankel-function of the 1st kind, resp., with im aginary arguments. The dimensionless real variable y is related to the radial coordinate r by

$$y = _{I}r; (15)$$

$$I = \frac{3}{\frac{2M}{h^2}} (B + jE j) :$$
 (16)

The two factors (i) and $\frac{1}{2}i^{1}$ are chosen so that the pair of solutions are simply related to the modied Bessel function of integer order $I_{l+\frac{1}{2}}(y)$ and $K_{l+\frac{1}{2}}(y)$ for which a number of rapidly converging series expansions exist (see R ef. [5], C hapt. 102)

$$f(i)^{l}j_{l}(iy); \quad \frac{1}{2}i^{l}h_{1}^{(1)}(iy)g = \begin{pmatrix} s & s & y \\ \frac{1}{2y}I_{l+\frac{1}{2}}(y); & \frac{1}{2y}K_{l+\frac{1}{2}}(y) \end{pmatrix}; \quad (17)$$

The radial function R (r) in region I thus has the general form

For $r > R_1$ (region 0), it is more convenient to deal with the di erential Eq. (10) for u(r) which has the form

$$\frac{h^2}{2M}u^{(0)}(r) + \frac{h^2l(l+1)}{2M}u^2 - \frac{Ze_0^2}{r}u = Eu:$$
(19)

We have to nd a normalizable solution of (19). It turns out that the only normalizable solution of (19) has the form

$$u(\mathbf{r}) = C_0 z_0^{l+1} U(a_0; b_0; z_0) e^{\frac{z_0}{2}};$$
 (20)

where the dimensionless variable z_0 is related to r by

$$z_0 = 2 r$$
 (21)

with

$$= \frac{\sum_{j=1}^{s} \frac{2M \pm j}{h^2}}{h^2}$$
(22)

and where $w = U(a_0; b_0; z_0)$ is a particular solution K um m er's di erential equation

$$z_0 \frac{d^2 w}{dz_0^2} + (b_0 - z_0) \frac{d w}{dz_0} = 0$$
: (23)

The parameters a_0 and b_0 in (23) are related to the parameters in Eq. (19) by

$$a_0 = \frac{2(l+1)}{2}$$
 (24)

$$b_0 = 2(1+1)$$
 (25)

$$d_0 = \frac{Z e_0^2}{h} \frac{2M}{f_{\rm E} j}$$
(26)

and the solution U $(a_0; b_0; z_0)$ of (23) is de ned as follows: Wewrite b_0 in the form

$$b_0 = 1 + n$$
; (27)

which implies

$$n = 2l + 1$$
: (28)

Then the function U $(a_0; 1 + n; z_0)$, where n = 1; ::: reads (see Ref. [5], Eq. (13.1.6) or Ref. [6], Eq. (13) of Chapt. 6.7.1)

$$U(a_{0};n+1;z_{0}) = \frac{(1)^{n-1}}{n!(a_{0} n)} fM(an+1;z_{0}) ln z_{0} + \frac{x^{1}}{a_{0}} \frac{(a_{0}) z_{0}}{(n+1)!} [(a_{0}+1) (1+1) (1+n+1)] + \frac{(n-1)!^{N-1}(a_{0} n)}{(a_{0})!} \frac{z_{0}}{a_{0}} \frac{(n-1)!^{N-1}(a_{0} n)}{(1+1)!} (29)$$

In (29), the function (x) is the logarithm ic derivative of the -function

$$(x) = \frac{d(x)}{dx} = (x) = \frac{d\ln(x)}{dx}$$
(30)

and (c) is Pochham m er's symbol

(c)
$$= c(c+1) ::: (c+1) = \frac{(c+1)}{(c)} :$$
 (31)

Furtherm ore, M $(a_0; b_0; z_0)$ is the con uent hypergeom etric function

$$M (a_0; b_0; z_0) = \frac{X^4}{a_0} \frac{(a_0 + a_0)}{(a_0)(b_0 + a_0)} \frac{z_0}{(a_0)(b_0 + a_0)} \frac{z_0}{a_0}$$
(32)

We note in passing that the complicated form of the solution (29) is due to the fact that the parameter b_0 in U ($a_0; b_0; z_0$) is an integer. For non-integer b_0 , the function U ($a_0; b_0; z_0$) depends in a simple way on two con uent hypergeometric functions (see Ref. [5], Eq. (13.1.3)). This form of U ($a_0; b_0; z_0$) becomes singular if b_0 tends to an integer value. The limiting process which leads to the form (29) is discussed in Ref. [6].

For any value of b_0 , the asymptotic behaviour of U for < (z_0) ! 1 is given by

$$U(a_{0};b_{0};z_{0})! \frac{1}{z_{0}^{a_{0}}} 1+0 \frac{1}{jz_{0}j}$$
(33)

(see Ref. [5], Eq. (13.1.8)). From (33) and (20) it is clear that u(r) is a normalizable function irrespectively of the value of the energy E. However, it turns out that the continuity conditions can only be met for certain discrete values of E. The radial function $R_0(r)$ in region 0 is thus dened by

$$R_{0}(r) = \frac{u(r)}{2r} = C_{0}(2r)^{1}U(a_{0};21+2;2r)e^{-r}:$$
(34)

Before we proceed to the explicit formulation of the continuity conditions, we return to the form of the solution in region I in the general case that the $r\{\text{dependent term } Z e_0^2 = ("_I r) \text{ is } \underline{not} \text{ neglected}$. Then the dimension for u (r) in region I has the form

$$\frac{h^2}{2M} \frac{d^2}{dr^2} = \frac{l(l+1)}{r^2} u + B = \frac{Z e_0^2}{"_{I}r} u = E u :$$
(35)

Eq. (35) resembles Eq. (19). In fact, with the replacements

$$Z ! \frac{Z}{\mathbf{u}_{I}};$$
(36)

Eq. (19) becomes Eq. (35).

W ith the ansatz

$$u(\mathbf{r}) = z_{I}^{l+1}w(z_{I})e^{-\frac{z_{I}}{2}}$$
 (38)

we obtain again K um m er's di erential equation for w (z)

$$z_{I}\frac{d^{2}w}{dz_{I}^{2}} + (b_{0} \quad \underline{z})\frac{dw}{dz_{I}} \quad \underline{a}w = 0; \qquad (39)$$

where b_0 is again given by (25) or (27), but a_I is obtained from a_0 by the replacements (36), (37):

$$a_{I} = \frac{2(l+1)}{2} \frac{d}{d};$$
 (40)

$$d_{I} = \frac{Z e_{0}^{2}}{"_{I}h} \frac{2M}{fE B j}$$
(41)

and the dimensionless variable z_I is related to r by

$$z_{I} = 2$$
 $\frac{2M}{h^{2}}$ $\frac{E}{r} = 2_{I}r$: (42)

The parameter $_{\rm I}$ de ned in (16) agrees with $2M = h^2$ JE B j because E < 0 and B > 0. The general solution w of Eq. (39) can be written as a linear combination of the function U (a_I;21+2;z_I) and, as linearly independent 2nd solution, the con uent hypergeom etric function M (a_I;21+2;z_I):

$$w (z_{I}) = A_{I}^{*}M (a_{I};2l+2;z_{I}) + B_{I}^{*}U (a_{I};2l+2;z_{I}) :$$
(43)

W e note that we had to suppress the solution M $(a_0; 2l+2; z_0)$ in region 0 because it would lead to a non-norm alizable solution.

The radial solution R (r) in region I thus assumes the form

$$R_{I}(r) = \frac{u(r)}{2_{I}r};$$
 (44)

$$R_{I}(r) = (2_{I}r)^{1}e^{-r} \quad A[M (a_{I};2l+2;2_{I}r) + B_{I}(a_{I};2l+2;2_{I}r)]:$$
(45)

W e now turn to the continuity conditions which enable us to determ ine the am plitudes A_{I} , B_{I} (or $\tilde{A_{I}}, \tilde{B_{I}}$), C_{0} , and the energy eigenvalues E . Once these parameters will be obtained, we shall norm alize the entire radial function to 1.

The radial wave function R (r) and its 1^{st} derivatives m ust be continuous at the lim its $r = R_2$ and $r = R_1$ of the regions II and I:

$$R_{II}(R_2) = R_{I}(R_2);$$
 (46)

$$\frac{\mathrm{dR}_{\mathrm{II}}(\mathrm{R}_{2})}{\mathrm{dR}_{2}} = \frac{\mathrm{dR}_{\mathrm{I}}(\mathrm{R}_{2})}{\mathrm{dR}_{2}}; \qquad (47)$$

$$R_{I}(R_{1}) = R_{0}(R_{1});$$
 (48)

$$\frac{\mathrm{dR}_{\mathrm{I}}(\mathbf{R}_{\mathrm{I}})}{\mathrm{dR}_{\mathrm{I}}} = \frac{\mathrm{dR}_{\mathrm{0}}(\mathbf{R}_{\mathrm{I}})}{\mathrm{dR}_{\mathrm{I}}} :$$
(49)

W e proceed as follows:

Eqs. (46) and (47) are 2 linear inhom ogeneous equations for the am plitudes A_{I}, B_{I} (or A_{I}, B_{I}). We solve them for these am plitudes and substitute the result into the equation

$$\frac{d\ln R_{1}(R_{1})}{dR_{1}} = \frac{d\ln R_{0}(R_{1})}{dR_{1}};$$
(50)

i.e. the ratio of the Eqs. (49) and (48). Eq. (50) represents a transcendental equation for the energy. It is solved num erically. The amplitude C_0 can subsequently be obtained from (48). The resulting wavefunction R (r) is not yet norm alized to 1. This can be easily achieved by the replacement

$$R(r) ! \tilde{R}(r) := N \qquad R(r) ; \qquad (51)$$

with

$$N = \frac{{\binom{8}{5}} z^{\frac{3}{2}}}{{\binom{9}{5}} \frac{1}{2}} \frac{{\binom{9}{5}} \frac{1}{2}}{{\binom{1}{5}}}; \qquad (52)$$

Let us present this procedure in m ore detail: W e introduce the abbreviations:

$$f_{1}^{(1)}(_{I}r) \qquad [f_{1}^{(1)}(x)]_{x=_{I}r} = \frac{1}{2x} I_{l+\frac{1}{2}}(x) \qquad ; \qquad (53)$$

$$f_{1}^{(2)}(_{I}r) \qquad [f_{1}^{(2)}(x)]_{x=_{I}r} := \frac{r}{2x} K_{1+\frac{1}{2}}(x)_{x=_{I}r}; \qquad (54)$$

$$\mathbf{f}_{1}^{(1)}(2_{I}r) \quad \mathbf{f}_{1}^{(1)}(y)_{y=2_{I}r} \coloneqq \bigvee_{p}^{n} e^{\frac{y}{2}} M (a_{I};2l+2;y)_{y=2_{I}r}^{1};$$
(55)

$$f_{1}^{(2)} (2 r) \qquad f_{1}^{(2)} (y)]_{y=2 r} \approx y^{1} e^{\frac{y}{2}} U (a_{1};2l+2;y) \Big|_{y=2 r} :$$
(56)

Furtherm one, we use the prime ' to denote the derivative with respect to the variable given as argument: $2 \qquad 3$

$$f_{1}^{(i) 0}(_{I}R_{2}) \coloneqq 4 \frac{df_{1}^{(i)}(x)}{dx}_{5}^{5};$$

$$f_{1}^{(i) 0}(2_{I}R_{2}) \coloneqq 4 \frac{df_{1}^{(i)}(y)}{dy}_{5}^{5};$$

$$j_{1}^{0}(_{II}R_{2}) \coloneqq \frac{dj_{1}(x)}{dx}_{5}^{*};$$

a.s.o.

From the continuity equations (46), (47) we nd the amplitudes A_{I} , B_{I} and A_{I} , B_{I} to be given by very sim ilar relations

$$A_{I} = \frac{j_{1}(I_{II}R_{2})f_{1}^{(2)0}(I_{I}R_{2}) - \frac{II}{I}f_{1}^{(2)}(I_{I}R_{2})j_{1}^{0}(I_{II}R_{2})}{W(f_{1}^{(1)};f_{1}^{(2)})]_{IR_{2}}};$$
(57)

$$B_{I} = \frac{j_{1}(I_{1}R_{2})f_{1}^{(1)}(I_{1}R_{2}) - I_{1}I_{1}^{(1)}(I_{1}R_{2})j_{1}^{(0)}(I_{1}R_{2})}{M(f_{1}^{(1)}(x);f_{1}^{(2)}(x))]_{x=I_{R_{2}}}$$
(58)

The W ronskian in the denom inators is given by (see Ref. [5], Eq. (102.8))

$$W (f_{1}^{(1)}(x); f_{1}^{(2)}(x)) \coloneqq f_{1}^{(1)}(x) f_{1}^{(2)}(x) \qquad f_{1}^{(2)}(x) f_{1}^{(1)}(x) = \frac{1}{2x^{2}};$$
(59)

$$A_{I}^{r} = \frac{j_{1}(I_{II}R_{2})f_{1}^{(2)0}(2I_{I}R_{2}) - \frac{II}{2I_{I}}f_{1}^{(2)}(2I_{I}R_{2})j_{1}^{0}(I_{II}R_{2})}{[N(f_{1}^{(1)}(Y);f_{1}^{(2)}(Y))]_{Y=2I_{R}}};$$
(60)

$$\mathbf{B}_{I}^{*} = \frac{\mathbf{j}_{I}(\mathbf{I}_{I}\mathbf{R}_{2})\mathbf{f}_{1}^{(1)}(\mathbf{2}_{I}\mathbf{R}_{2}) - \frac{\mathbf{I}_{I}}{2\mathbf{I}_{I}}\mathbf{f}_{1}^{(1)}(\mathbf{2}_{I}\mathbf{R}_{2})\mathbf{j}_{1}^{0}(\mathbf{I}_{I}\mathbf{R}_{2})}{\mathbf{N}(\mathbf{f}_{1}^{(1)}(\mathbf{y});\mathbf{f}_{1}^{(2)}(\mathbf{y}))\mathbf{j}_{Y=2}\mathbf{I}_{R_{2}}} :$$
(61)

The W ronskian in the denom inators of (60) and (61) can be related to the W ronskian W (M $(a_I; 2l+2; y); U (a_I; 2l+2; y))$:

Using the dierential Eq. (39), one nds for W (M;U) (see Ref. [5], Eq. (13.1.22))

$$\mathbb{W} \ (M \ (a_{I};2l+2;y);U \ (a_{I};2l+2;y)) = \frac{(2l+2)}{(a_{I})^{2l+2}}$$
(63)

and thus for \mathbb{W} $(\mathbf{f}_{1}^{(1)}(\mathbf{y});\mathbf{f}_{1}^{(2)}(\mathbf{y})):$

$$W (f_{1}^{(1)}(y); f_{1}^{(2)}(y)) = \frac{(21+2)}{(a_{1})^{2}y};$$
(64)

Substituting (59) into (57) and (58) and, analogously, substituting (64) into (60) and (61) we obtain the following forms of the amplitudes in region I:

$$A_{I} = \frac{2 {}_{I}^{2} R_{2}^{2}}{j_{1}} ({}_{II} R_{2}) f_{1}^{(2) 0} ({}_{I} R_{2}) - \frac{\pi}{I} f_{1}^{(2)} ({}_{I} R_{2}) j_{1}^{0} ({}_{II} R_{2}) ; \qquad (65)$$

$$B_{I} = \frac{2 {}_{I}^{2} R_{2}^{2}}{j_{1}} ({}_{II} R_{2}) f_{1}^{(1) 0} ({}_{I} R_{2}) - \frac{\pi}{I} f_{1}^{(1)} ({}_{I} R_{2}) j_{1}^{0} ({}_{II} R_{2}) ;$$
(66)

$$\mathbf{A}_{\mathrm{I}}^{\prime} = \frac{4 \, {}_{\mathrm{I}}^{2} \mathbf{R}_{2}^{2} \, (\mathbf{a}_{\mathrm{I}})}{(21+2)} \, \mathbf{j}_{\mathrm{I}}^{\prime} (\, {}_{\mathrm{II}} \mathbf{R}_{2}) \mathbf{f}_{\mathrm{I}}^{\prime^{(2)} \, 0} (2 \, {}_{\mathrm{I}} \mathbf{R}_{2}) - \frac{\pi}{2} \mathbf{f}_{\mathrm{I}}^{\prime^{(2)}} (2 \, {}_{\mathrm{I}} \mathbf{R}_{2}) \mathbf{j}_{\mathrm{I}}^{0} (\, {}_{\mathrm{II}} \mathbf{R}_{2}) \, ; \qquad (67)$$

$$\mathbf{B}_{\mathrm{I}}^{\prime} = \frac{4 \, {}_{\mathrm{I}}^{2} \mathbf{R}_{2}^{2} \, (\mathbf{a}_{\mathrm{I}})}{(2 + 2)} \, \mathbf{j}_{\mathrm{I}}^{\prime} (\, {}_{\mathrm{II}} \mathbf{R}_{2}) \mathbf{f}_{\mathrm{I}}^{\prime(1)} \, {}^{0} (2 \, {}_{\mathrm{I}} \mathbf{R}_{2}) - \frac{\pi}{2} \mathbf{f}_{\mathrm{I}}^{\prime(1)} \, {}^{0} (2 \, {}_{\mathrm{I}} \mathbf{R}_{2}) \mathbf{j}_{\mathrm{I}}^{0} (\, {}_{\mathrm{II}} \mathbf{R}_{2}) : \tag{68}$$

W ith (65), (66) or (67), (68) the amplitudes of the 2 linearly independent solutions in region I are represented as a function of the energy E. The eigenvalues can now be obtained from the ratio of the two continuity conditions (49) and (48), i.e. from the equation

$$\frac{d\ln R_{I}(\mathbf{r})}{d\mathbf{r}}\Big|_{\mathbf{r}=R_{1}} = \frac{d\ln R_{0}(\mathbf{r})}{d\mathbf{r}}\Big|_{\mathbf{r}=R_{1}} :$$
(69)

This is a transcendental equation for the eigenenergies. It has in nitely many solutions close to the energy E = 0 due to the "in nite range" of the Coulomb potential. In spite of the complicated nature of the wavefunctions it is not dicult to nd the num erical solutions of (69). More explicitly, the logarithm ic derivatives in (69) look as follows:

$$\frac{d\ln R_{0}(r)}{dr} \Big|_{r=R_{1}}^{\#} = \frac{\left(\frac{d}{dr}(2 r)^{l}U(a_{0};2l+2;2 r)e^{-r}\right)}{(2 r)^{l}U(a_{0};2l+2;2 r)e^{-r}} \Big|_{r=R_{1}}^{\#}$$
(70)

$$\frac{d \ln R_{I}(\mathbf{r})}{d\mathbf{r}} = \frac{4 \frac{d}{d\mathbf{r}} (A_{I} f_{1}^{(1)}(\mathbf{r}) + B_{I} f_{1}^{(2)}(\mathbf{r}))}{A_{I} f_{1}^{(1)}(\mathbf{r}) + B_{I} f_{1}^{(2)}(\mathbf{r})} = (71)$$

$$\frac{d\ln R_{I}(\mathbf{r})}{d\mathbf{r}}^{\#} = \frac{4}{\frac{d}{d\mathbf{r}}} \frac{\frac{d}{d\mathbf{r}} \left(\tilde{R}_{I} \tilde{\mathbf{f}}_{1}^{(1)}(\mathbf{r}) + \tilde{B}_{I} \tilde{\mathbf{f}}_{1}^{(2)}(\mathbf{r}) \right)}{\tilde{R}_{I} \tilde{\mathbf{f}}_{1}^{(1)}(\mathbf{r}) + \tilde{B}_{I} \tilde{\mathbf{f}}_{1}^{(2)}(\mathbf{r})} \frac{3}{\mathbf{r}_{R_{1}}}$$
(72)

Eq. (72) and (71) deal with the case of the exact potential and of the approximate constant potential in region I. In calculating the derivative $f_1^{(i) 0}(\mathbf{r})$ or $f_1^{(i) 0}(\mathbf{r})$ one can use properties of the di erent functions involved.

Having determ ined the eigenvalues from Eq. (69) one obtains the amplitude C₀ from Eq. (48) and thereafter the correct norm alization of the entire function must be achieved by num erical calculation of the norm alization constant (52).

3 Polarization e ects in a macroscopic description

In Sec.2, only the polarization of the insulator which is produced by a constant positive surface charge density $Ze_0=(4 R_2^2)$ on the surface S_2 of the metal was taken into account. However, the charge distribution $_{\rm e}(\mathbf{r})$ of the externally localized electrons produces not only additional polarization elects in the insulating surface layer but also modiles the distribution of the positive surplus charge on the surface S_2 of the metal. In this section, we present a simple macroscopic description of the polarization elects which is based on M axwell's equations in the presence of hom ogeneous dielectric media.

Outside of the metallic core, i.e. in the region I ($R_2 < r < R_1$) of the insulator, and in the vacuum O ($r > R_1$) surrounding the insulator the "electric eld" E and the "displacement" D are related by:

$$\vec{D}(\mathbf{r}) = \mathbf{I}_{I}\vec{E}(\mathbf{r}) = (1+4 \quad I)\vec{E}(\mathbf{r}) \quad \text{for } \mathbf{R}_{2} < \mathbf{r} < \mathbf{R}_{1} \quad \text{region I};$$
(73)

$$D'(\mathbf{r}) = \mathbf{E}'(\mathbf{r}) \qquad \text{for } \mathbf{r} > \mathbf{R}_1 \quad \text{region 0} \quad ; \tag{74}$$

where $"_{I}$ and $_{I}$ are the "dielectric constant" and the "electric susceptibility" of the insulator, respectively. The elds satisfy M axwell's equations

div
$$D' = 4_{e}(\mathbf{r})$$
; (75)

$$\operatorname{rot} \mathbf{E} = 0 : \tag{76}$$

For the sake of simplicity, we assume that the distribution $_{e}(\mathbf{r})$ of the externally located electrons and, as a consequence, also the positive surface charge distribution $_{S_2}(\mathbf{r})$ on S_2 , are <u>azim uthally symmetric</u>, i.e. that they depend only on the polar angle # and the radial coordinate r. They can thus be written in the form

$${}_{e}(\mathbf{x}) = {}_{e}(\mathbf{x}; \#) = \sum_{l=0}^{X^{l}} {}_{l}(\mathbf{x}) Y_{l0}(\#) ;$$
(77)

$$_{S_{2}}(\boldsymbol{x}) = _{S_{2}}(R_{2};\boldsymbol{\#}) = \sum_{l=0}^{N^{2}} Y_{l0}(\boldsymbol{\#}) :$$
 (78)

Integrating the surface charge density over the surface S_2 m ust yield the total positive surface charge Z e_0 . This implies the condition

$$Z e_0 = d^3 r (r R_2)_{S_2} (R_2; \#)$$
 (79)

or,with (78)

 $\sum_{l=0}^{S_2} = \frac{p \frac{Z e_0}{4 R_2^2}}{R_2^2} :$ (80)

The components $_1(\mathbf{r})$ of the electronic charge distribution are related to the total electronic charge distribution by

$$\int_{1}^{2} (\mathbf{r}) = 2 \qquad d\# \sin \# _{e} (\mathbf{r}; \#) Y_{10} (\#) :$$
(81)

The Maxwell equations (75) and (76) are equivalent to the Poisson equation

$$I_{I}(\mathbf{r}; \#) = \frac{4}{\mathbf{u}_{I}} e(\mathbf{r}; \#)$$
 (82)

in region I and to

$$_{0}(\mathbf{r}; \#) = 4_{e}(\mathbf{r}; \#)$$
 (83)

in region 0. Here, the potential

$$(r; \#) = _{I}(r; \#) \quad \text{for } R_{2} < r < R_{1};$$
 (84)

$$(r; \#) = _{0} (r; \#)$$
 for $r > R_{1}$ (85)

is related to the electric eld E by

$$\mathbf{\tilde{E}} = \tilde{\mathbf{r}} :$$
 (86)

The following boundary conditions m ust be fulled at the surfaces $S_{\rm 2}$ and $S_{\rm 1}$:

$$"_{I} \frac{@_{I}(R_{2};\#)}{@R_{2}} = 4 \qquad S_{2}(R_{2};\#)$$
(87)

$$\frac{\theta_{1}(\mathbb{R}_{2};\#)}{\theta_{2}^{*}} = 0$$
(88)

$$_{I}(\mathbb{R}_{1};\#) = _{0}(\mathbb{R}_{1};\#):$$
(90)

Furtherm ore, the potential $_0$ (r;#) must satisfy the asymptotic condition

$$_{0}(r;\#) ! 0 \frac{1}{r} :$$
 (91)

The conditions (87) and (89) are obtained from the M axwell equation (75), and the conditions (88) and (90) result from (76) and the requirement that the classical electric eld should be everywhere nite.

The solutions $_{\rm I}$ and $_{\rm 0}$ of the Poisson equations (82) and (83) in the regions I and 0, respectively, can be written in the form :

$$I(\mathbf{r}; \#) = \frac{1}{\mathbf{n}_{I}} (\mathbf{r}; \#) + \mathbf{n}_{I} (\mathbf{r}; \#) ; \qquad (92)$$

$$_{0}(\mathbf{r}; \#) = (\mathbf{r}; \#) + \prime_{0}(\mathbf{r}; \#); \qquad (93)$$

where (r; #) is the C oulom b potential produced by the electronic charge distribution $_{e}(x^{0}; \#^{0})$

$$(\mathbf{r}; \#) \coloneqq \overset{Z}{=} \mathrm{d}^{3} \mathbf{r}^{0} \underbrace{\mathrm{e}^{(\mathbf{r}^{0}; \#^{0})}}_{j\mathbf{r}} \underbrace{\mathrm{e}^{\mathbf{j}}}_{\mathbf{r}^{0}j} : \qquad (94)$$

The charge distribution $_{e}(\mathbf{r})$ itself is to be calculated from the wavefunctions of the bound and predom inantly externally located (i.e. in region 0, $\mathbf{r} > R_{1}$) electrons. The "conduction electrons" which are located internally (i.e. in region II, $\mathbf{r} < R_{2}$) do not contribute to $_{e}(\mathbf{r})$ because they are already taken into account by the number Z of positive surplus charges. The density $_{e}(\mathbf{r})$ is thus mainly located in region 0 and it is very small in region I, i.e. inside of the insulating surface layer, because the eigenenergies of the electrons are far below the positive barrier in region I.

The function ' $_{\rm I}(r;\#)$ is the general azim uthally sym m etric solution of the Laplace equation in region I

$$Y_{I}(\mathbf{r}; \#) = \sum_{l=0}^{N^{l}} C_{l}^{I} \mathbf{r}^{l} + \frac{D_{l}^{I}}{\mathbf{r}^{l+1}} Y_{l0}(\#)$$
(95)

and $'_0$ (r;#) the corresponding most general solution of the Laplace equation in region 0 satisfying in addition the asymptotic condition (91):

$$'_{0}(\mathbf{r}; \#) = \sum_{l=0}^{\lambda^{2}} \frac{D_{1}^{0}}{\mathbf{r}^{l+1}} Y_{l0}(\#) :$$
(96)

The Coulom b potential (r; #) can be written as

$$(\mathbf{r}; \#) = \frac{\lambda^{\underline{k}}}{\sum_{\underline{l}=0}^{\underline{k}}} \frac{4}{2\underline{l}+1} \quad a_{\underline{l}}(\mathbf{r})\mathbf{r}^{\underline{l}} + \frac{b_{\underline{l}}(\mathbf{r})}{\mathbf{r}^{\underline{l}+1}} \, Y_{\underline{l}\underline{0}}(\#); \qquad (97)$$

where the functions $a_1(r)$ and $b_1(r)$ are related to the components $_1(r)$ of the electronic charge distribution by

$$a_1(r) \coloneqq dr_1^0(r^0) r^{1};$$
 (98)

$$b_{1}(\mathbf{r}) := \int_{0}^{2\mathbf{r}} d\mathbf{r}^{0} {}_{1}(\mathbf{r}^{0}) {\mathbf{r}}^{0+2} :$$
 (99)

r

Substituting the explicit form s (95) to (97) into the boundary conditions (87), (89), and (90), we obtain the relations

$$\overset{X^{1}}{=0} \left(\frac{4}{(2l+1)^{n}} a_{1}(R_{2}) \mathbb{R}_{2}^{\frac{1}{2}-1} \frac{b_{1}(R_{2})(l+1)}{R_{2}^{\frac{1+2}{2}}} + C_{1}^{\frac{1}{2}} \mathbb{R}_{2}^{\frac{1}{2}-1} \right) \\
- \frac{D_{1}^{\frac{1}{2}} (l+1)}{R^{\frac{1+2}{2}}} + \frac{4}{n} \frac{S_{2}}{1} Y_{10}(\#) = 0;$$
(100)

$$\mathbf{"}_{I} \overset{\overset{}}{\underset{l=0}{\overset{}}_{0}} C_{1}^{I} \mathbb{I} \mathbb{R}_{1}^{1-1} \qquad \frac{D_{1}^{I}}{\mathbb{R}_{1}^{1+2}} \overset{(l+1)}{\underset{l=0}{\overset{}}_{0}} + \frac{D_{1}^{0}}{\mathbb{R}_{1}^{1+2}} \overset{(l+1)}{\underset{l=0}{\overset{}}_{I}} Y_{l0} (\#) = 0 ; \qquad (101)$$

$$X^{l} = 0 \qquad C_{1}^{I}R_{1}^{1} + \frac{D_{1}^{I}}{R_{1}^{l+1}} = \frac{D_{1}^{0}}{R_{1}^{l+1}} \qquad Y_{10} (\#) = 0 :$$
(102)

Furthermore, using the identity (see for instance Ref. [5]) for l 1

$$\sin \# \frac{dY_{10}}{d\#} = \frac{1(1+1)}{21+1} \frac{\Psi_{1+1,0}}{21+3} = \frac{\Psi_{1-1,0}}{21-1}$$
(103)

щ

together with (92), (93) and (95), the condition (88) can be shown to be equivalent to the relation !

$$\frac{4}{(2l+1)''_{I}} = a_{1}(R_{2})R_{2}^{1} + \frac{b_{1}(R_{2})}{R_{2}^{1+1}} + C_{1}^{I}R_{2}^{1} + \frac{D_{1}^{I}}{R_{2}^{1+1}} = 0 ; \qquad (104)$$

where 1 1. Eq. (104) is seen to imply that the potential $_{I}(r; \#)$ is constant on the surface S_2 .Forl= 0, we obtain from (100)

$$D_{0}^{I} = \frac{4}{"_{I}} \left[b_{0}(R_{2}) + R_{2}^{2} b_{0}^{S_{2}} \right]$$
(105)

and from (101) and (102) the relations

$$"_{I}D_{0}^{I} = D_{0}^{0}$$
; (106)

$$C_{0}^{I} + \frac{D_{0}^{I}}{R_{1}} = \frac{D_{0}^{0}}{R_{1}} :$$
 (107)

Hence, with (105), we nd

$$C_{0}^{I} = \frac{("_{I} \ 1)4}{"_{I}R_{1}} \left[b_{0}(R_{2}) + R_{2}^{2} b_{0}^{S_{2}} \right]$$
(108)

and

$$D_{0}^{0} = 4 [b_{0}(R_{2}) + R_{2}^{2} b_{0}^{S_{2}}]:$$
(109)

For 1, we obtain from (100) and (104):

$$C_{1}^{I} = \frac{4}{(2l+1)!'_{I}} a_{1}(R_{2}) + \frac{s_{2}}{R_{2}^{1}} ; \qquad (110)$$

$$D_{1}^{I} = \frac{4}{(2l+1)''_{I}}^{h} \quad b(R_{2}) + \int_{1}^{S_{2}} R_{2}^{l+1}^{i} : \qquad (111)$$

For the coe cients D 0_1 , we nd the relations

$$D_{1}^{0} = C_{1}^{I}R_{1}^{2I+1} + D_{1}^{I}$$
(112)

and

$$D_{1}^{0} = \mathbf{"}_{I} \qquad C_{1}^{I} \quad \frac{1}{(l+1)} R_{1}^{2l+1} + D_{1}^{I}$$
(113)

from the Eqs. (102) and (101), which hold for 1 - 0.

The equality of the righthand sides of (112) and (113) together with (110) and (111) yields a condition for the surface charge components ${}_{1}^{S_{2}}$ for l 1. From this equation one nds the explicit form

$$R_{1}^{S_{2}} = R_{2}^{1} \frac{1}{\frac{1}{1+1}} a(R_{2}) \frac{1}{1+1} u_{I} + 1 + b_{1}(R_{2})R_{1} \frac{(2l+1)}{1+1} u_{I} + 1 + b_{1}(R_{2})R_{1} \frac{(2l+1)}{1+1} u_{I} + 1 + b_{1}(R_{2})R_{1} \frac{(2l+1)}{1+1} u_{I} \frac{(2l+1)}{1+1}$$

for 1 1. The component $_{0}^{S_{2}}$ is determined by the conservation of the total positive charge on S_{2} and is given by Eq. (80).

For 1, one obtains from (110), (111) and (113)

$$D_{1}^{0} = \frac{4}{(2l+1)} \left(\frac{1}{l+1} R_{1}^{2l+1} a_{1}(R_{2}) - b_{1}(R_{2}) + \frac{s_{2}}{l} - \frac{1}{l+1} \frac{R_{1}^{2l+1}}{R_{2}^{1}} + R_{2}^{2l+2} \right)$$
(115)

A swe have m entioned already, the charge distribution $_{e}(r; #)$ of the externally located electrons is vanishingly sm all for $r < R_{1}$. Consequently, we have

$$b_1(r) = 0$$
 for $r < R_1$ (116)

• •

and

$$a_1(r) = q(R_1)$$
 for $r < R_1$: (117)

The potentials $_{0}(\mathbf{r})$, $_{I}(\mathbf{r})$, $_{II} = _{I}(\mathbb{R}_{2})$, and the charge distribution $_{S_{2}}(\mathbb{R}_{2}; \#)$ on the surface S_{2} are thus fully determ ined for a given azim uthally sym metric distribution $_{e}(\mathbf{r}; \#)$ of the externally located electrons.

The potential ∇ (r) acting on an electron in our "m esoscopic atom " is related to the potential functions as follow s:

$$\vec{\nabla} (\mathbf{r}; \#) = \mathbf{e}_{\Pi} \quad V_{\Pi}^{0} = \mathbf{e}_{\Pi} (\mathbf{R}_{2}) \quad V_{\Pi}^{0} \quad \text{for } \mathbf{r} < \mathbf{R}_{2} ; \qquad (118)$$

$$\tilde{V}(r; \#) = \Theta_{I}(r; \#) + B_{0}$$
 for $R_{2} < r < R_{1}$; (119)

$$\nabla (\mathbf{r}; \#) = \Theta_0 (\mathbf{r}; \#) \qquad \text{for } \mathbf{r} > \mathbb{R}_1 \text{ (region 0) : } (120)$$

The potential (V_{II}^0) represents the interaction of a conduction electron with the average ionic background charge in the m etal and has to be added to the constant potential Q_{II} produced by the positive surplus charge on S_2 . The potential barrier B_0 to be added in the insulating surface layer is related to the average energy gap between the electronic bands. Since it is of quantum m echanical origin, it is not contained in the classically determ ined term $Q_{II}(r; \#)$.

The Schrödinger equation with the potential ∇ (r;#) can no longer be solved analytically. One could diagonalize the Ham iltonian

$$\hat{H} = \frac{h^2}{2M} + \nabla (r; \#)$$
 (121)

within the set of analytical eigenfunctions which we have determ ined in Sec.2. This represents a selfconsistency problem, because the eigenfunctions of the H am iltonian (121) depend on the charge distribution $_{\rm e}$ (r) which is calculated from them. The solution thus requires an iteration process.

Let us consider two special cases for which the results of this section simplify considerably:

1. If we neglect the polarization e ects produced by the external electrons, that is if we put

$$_{e}(x) = 0;$$
 (122)

the quantities $a_1(r)$, $b_1(r)$ vanish for 1 0, and, as a consequence, so do the components ${}_{1}^{S_2}$. The positive surplus charge density on S_2 is then spherically symmetric and given by

$$S_2$$
 (r;#) = ${}_0^{S_2}Y_{00} = \frac{Ze_0}{4R_2^2}$: (123)

It is easily seen that, in this case, the potential V (r; #) becomes equal to the potential V (r) we considered in Sec. 2.

2. If we assume that the charge density $_{e}(\mathbf{r})$ of the external electrons is spherically sym – metric

$$_{e}(\mathbf{r}) = _{e}(\mathbf{r});$$
 (124)

only the component l=0 (r) in (77) is unequal 0

$$_{1}(\mathbf{r}) = _{10} \quad \frac{p}{4} \quad _{e}(\mathbf{r})$$
 (125)

and, consequently, the quantities $a_1(r)$, $b_1(r)$, and $\begin{pmatrix} s_2 \\ 1 \end{pmatrix}$ vanish for l = 1. In this case, the potentials π , π and π take the following form

$$_{II} = _{I}(R_{2})$$
 (for $r < R_{2}$); (126)

$$I(\mathbf{r}) = a_0(\mathbf{r}) + \frac{b_0(\mathbf{r})}{\mathbf{r}} \cdot \frac{\mathbf{p}}{4} + \frac{(\mathbf{u}_{\mathrm{I}} \ 1)\mathbf{Z} \mathbf{e}_0}{\mathbf{u}_{\mathrm{I}}} + \frac{\mathbf{Z} \mathbf{e}_0}{\mathbf{u}_{\mathrm{I}}\mathbf{r}} \quad \text{(for } \mathbf{R}_2 < \mathbf{r} < \mathbf{R}_1\text{) ; (127)}$$

$$a_{0}(\mathbf{r}) = a_{0}(\mathbf{r}) + \frac{b_{0}(\mathbf{r})}{\mathbf{r}} \frac{\mathbf{p}}{4} + \frac{\mathbf{Z} \mathbf{e}_{0}}{\mathbf{r}} \quad \text{(for } \mathbf{r} > \mathbf{R}_{1}\text{)}:$$
(128)

The case of a spherically sym m etric distribution of the externally located electrons is realistic at nite tem perature, because m agnetic substates of a given electronic level are expected to be occupied with the sam e probability whenever the m esoscopic atom is in contact with a therm al reservoir of nite tem perature.

The functions a_0 (r) and b_0 (r) depend them selves on the electronic distribution. For r R_1 , a_0 (r) decreases to zero as one can see from (98). The quantity $\frac{1}{4}$ b_0 (r) represents the total charge of the externally located electrons inside the sphere of radius r

$$Q_{e}(\mathbf{r}) \coloneqq \int_{0}^{Z^{r}} dr^{0}r^{02} d = (r^{0}; \#^{0}) :$$
 (129)

Using (77) in (129) we nd

$$p \frac{1}{4} b_0(\mathbf{r}) = Q_e(\mathbf{r})$$
: (130)

For $r >> R_1$, p_{--} by (r) tends to the total charge $Q_e(1)$ of the externally located electrons.

If the mesoscopic atom is neutral, i.e. if there are as many externally bound electrons as there are positive surplus charges on the surface S_2 of the metallic core, the term $b_0(r)^{-1} = r$ in Eq. (128) cancels the potential Z = 0 = r for r R_1 , as it should.

Let us study the asymptotic behaviour of the function $a_0(r)$ and $b_0(r)$ for r ! 1 : For simplicity, let us assume that only the lowest external electron state is occupied by two electrons,

one with intrinsic spin up and the other one with spin down. The external state of lowest energy belongs necessarily to orbital angular momentum (l = 0) and to zero number of radial modes. We assume that the wavefunctions we determ ined in Sec. 2 are realistic for $r = R_1$. In region 0, the electronic density distribution is then given by

$$_{e}(\mathbf{r}) = (\mathbf{\varphi}) \quad 2\mathbf{\hat{R}}_{=0}(\mathbf{r};\mathbf{E}) \mathbf{Y}_{00}^{2} = \frac{(\mathbf{\varphi})}{2} \quad \frac{\mathbf{u}_{=0}(\mathbf{2} \mathbf{r})}{2 \mathbf{r}}^{\frac{1}{2}}$$
 (131)

or, substituting the explicit wavefunction (20), by

$$e(\mathbf{r}) = \frac{(e_0)}{2} C_0^2 N^2 U^2 \frac{2}{2} \frac{d_0}{2}; 2; 2 \mathbf{r} e^{2\mathbf{r}}:$$
(132)

Here, N is the overall norm alization constant introduced by Eq. (52).

For z_0 1, the function U (a_0 ; b_0 ; Z_0) can be replaced by (see Ref. [5], Eq. (13.5.2))

$$U(a_{0};b_{0};z_{0})_{z_{0}-1} \quad \frac{1}{z_{0}^{a_{0}}} \left(1 + \frac{x^{1}}{n} \frac{(a_{0})_{n}(1 + a_{0} - b_{0})_{n}}{n!} - \frac{1}{z_{0}}\right)^{n} \quad (133)$$

Retaining only the 1^{st} term in (133), we obtain for the asymptotic density (2 r 1)

$$e^{(r)} - \frac{(e_{0})(C_{0}N_{0})^{2}}{2} (2 r)^{d_{0}} e^{2 r}$$
 (134)

and for the function $a_0(r)$

$$a_{0}(\mathbf{r}) \qquad p - \frac{z^{2}}{4} d\mathbf{r}^{0} \mathbf{r}^{0} e^{(\mathbf{r}^{0})} = \frac{(e^{2})(C_{0}N_{0})^{2}}{p - (2_{0})^{2}} dz_{0}(z_{0})^{d_{0}} e^{-2} e^{-2}$$
(135)

The integral in (135) is the "incomplete -function" (see Ref. [5], Eq. (6.5.3), Re(a) > 0)

$$(a;x) \coloneqq dtt^{a} \stackrel{t}{=} t$$
(136)

with the asymptotic expansion (Ref. [5], Eq. (6.5.32)

(a;x)
$$x^{a} = x^{a} + \frac{a}{x} + \frac{a}{x^{2}} + \frac{a}{x^{2}$$

From (135) { (137), we obtain a_0 (r) in the form

$$a_{0}(\mathbf{r}) = \frac{(\mathbf{e})(\mathbf{C}_{0}\mathbf{N})^{2}}{(\mathbf{2})^{2}}(\mathbf{2} \mathbf{r})^{d_{0}} e^{2\mathbf{r}}$$
(138)

for 2 r 1.

Of course, one could raise the accuracy of the result (138) by incorporating one or two more terms in (133) and (137). The important point, however, is that a_0 (r) tends to zero exponentially for large values of R_1 . This justices the assumption that the electronic charge density $_{\rm e}$ (r) in the asymptotic regime r R_1 is correctly described by the wavefunctions of Sec. 2, which do not contain the electronic polarization elects.

The function b_0 (r) can be written in the form (see (99))

$$b_{0}(\mathbf{r}) = \stackrel{p}{\underbrace{4}}_{0} \frac{z^{2}}{dr^{0}r^{\infty}} e^{(\mathbf{r}^{0})} \stackrel{p}{\underbrace{4}}_{r} \frac{z^{2}}{dr^{0}r^{\infty}} e^{(\mathbf{r}^{0})}; \qquad (139)$$

with

$$\int_{0}^{2^{1}} dr^{0}r^{0}r^{0} = \frac{p}{4} \int_{0}^{2^{1}} dr^{0}r^{0}r^{0} = \frac{Q_{e}(1)}{p} = \frac{Q_{e}(1)}{4} :$$
(140)

The 2nd term one the r.h.s. of (139) is easily seen to have the approximate form

$$\int_{0}^{\mathbb{Z}^{4}} dr^{0} r^{02} {}_{0} (r^{0}) \frac{(e_{0}) (C_{0}N)^{2}}{p - (2)^{3}} (2 r)^{d_{0}} e^{2 r}$$
(141)

for 2 r 1.

Thus the function b_0 (r) is asymptotically (2 r 1) given by

$$b_{0}(\mathbf{r}) = \frac{Q_{e1}(1)}{P_{4}} + \frac{e_{0}(C_{0}N)^{2}}{P_{4}(2)^{3}} (2 \mathbf{r})^{d_{0}} e^{2\mathbf{r}}; \qquad (142)$$

which m eans that it approaches exponentially the asymptotic value $Q_e(1) = \frac{p}{4}$.

In the general case of a #-dependent electronic charge density $_{e}(r; #)$, the quantities $a_{l \neq 0}(r)$ and $b_{l \neq 0}(r)$ are dimensional terms from zero and their asymptotic behaviour can be investigated in an analogous way. One modes that $a_{l > 0}(r)$ tends exponentially to zero and $b_{l > 0}(r)$ exponentially to constant values as r goes to in mity. Therefore, at large values of r, the dominant part of the potential V(r; #) is the potential V(r) given by Eq. (6). Thereby, our assumption that the wavefunctions determined in Sec. 2 are essentially correct at large values of r is seen to be justified.

For non-asym ptotic values of r, the electronic charge density and the resulting functions a_0 (r) and b_0 (r) must be obtained from the eigenfunctions of the H am iltonian (120) which contains the potential ∇ (r;#) de ned in (118) to (120). Let us form ulate the special case of a spherically sym m etric charge density and the resulting spherically sym m etric potential ∇ (r) in som ew hat m ore detail:

The electronic charge density at a nite tem perature T is given by

or, using the relation (see for instance Ref. [7], Eq. (3.69))

$$\sum_{m=1}^{X^{1}} \sum_{m=1}^{Y_{1m}} (\#;')^{2} = \frac{(2l+1)}{4}$$
 (144)

by

$$e(\mathbf{r}) = e_{n=1}^{\chi^{4}} \sum_{l=0}^{\chi^{4}} \frac{(2l+1)}{2} = \frac{1}{\exp \frac{E_{nl}}{T} + 1} e_{r}^{2} \hat{\mathbf{R}}(\mathbf{r}; \mathbf{E}_{nl}) :$$
(145)

Here, E_{n1} is the n-th eigenvalue for given angular m on entum land $R_1(r; E_{n1})$ is the corresponding eigenfunction of the radial Schrödinger equation. The parameter represents the chemical

potential which corresponds to the number of externally located electrons. The potential ∇ (r;#) has the form

$$\vec{\nabla} (\mathbf{r}) = \mathbf{e}_{\mathrm{I}} (\mathbf{R}_2) \quad V_{\mathrm{II}}^0 \qquad \text{for } \mathbf{r}_2 < \mathbf{R}_2 ;$$
 (146)
$$\vec{\nabla} (\mathbf{r}) = \mathbf{e}_{\mathrm{I}} (\mathbf{r}) + \mathbf{B}_0$$

$$= B_{0} \quad \bigoplus_{I} \frac{4}{\mathbf{u}_{I}} \quad a_{0}(\mathbf{r}) + \frac{b_{0}(\mathbf{r})}{\mathbf{r}} + C_{0}^{I} + \frac{D_{0}^{I}}{\mathbf{r}} Y_{00} \qquad \text{for } R_{2} < \mathbf{r} < R_{1}; \quad (147)$$

$$\nabla (\mathbf{r}) = \Theta_{0}(\mathbf{r}) = \Theta_{0}(\mathbf{r}) = \Theta_{0}(\mathbf{r}) + \frac{b_{0}(\mathbf{r})}{\mathbf{r}} + \frac{D_{0}^{0}}{\mathbf{r}} Y_{00} \quad \text{for } \mathbf{r} > R_{1};$$
 (148)

where D_0^{I} , C_0^{I} , and D_0^{0} are given by the Eq. (105), (108), and (109), resp. The functions a_0 (r) and b_0 (r) are defined by (98) and (99), where $_0 (r^0) = 4 e_e (r^0)$. The wavefunctions $R_1(r; E_{n1})$ are solutions of the radial Schrödinger equation with ∇ (r) given by (146) - (148)

$$\frac{h^2}{2M} \frac{d^2}{dr^2} + \frac{2}{r} \frac{d}{dr} - \frac{l(l+1)}{r^2} + \tilde{\nabla}(r) = E_{nl} \tilde{R}_1(r; E_{nl})_1 :$$
(149)

Since ∇ (r) depends itself on the functions $\mathbb{R}_1(r;\mathbb{E}_{n1})$, one has to solve (149) by iteration. One way to nd the solutions $\mathbb{R}_1(r;\mathbb{E}_{n1})$ of (149) is to expand the solutions $\mathbb{R}_1(r;\mathbb{E}_{n1})$ in terms of the radial eigenfunctions $\mathbb{R}_1(r;\mathbb{E}_0)$ de ned in Sec. 2, where the potential V (r) is given by Eq. (5) and related to ∇ (r) by

$$V(\mathbf{r}) = \lim_{e(\mathbf{r})! = 0} \tilde{V}(\mathbf{r})$$
 (150)

$$\tilde{R}_{1}(r;E_{n1}) = C R_{1}(r;E)$$
(151)

E are the eigenvalues obtained in Sec.2. In Eq. (151) we left away the basis functions $R_1(r; E)$ corresponding to continuous eigenvalues E of Eq. (9). Substitution of (151) into (149) leads to a nonlinear system of equations for the expansion coe cients c which must be solved by iteration.

4 Results

(

We present results on the spectrum of eigenenergies, the eigenfunctions, and on the electrom agnetic transition rate between externally and internally localized states for a range of values of the parameters R_1 , R_2 , and "_I. So far, we have not taken into account the e ects presented in Sec. 3, i.e. the polarization of the insulating dielectric material by externally localized electrons. The additional potential produced by this polarization is expected to modify the wave functions in the vicinity of the surface S_1 , perhaps even rather substantially. At large distances (say a couple of Angstrom outside of the surface S_1), the additional polarization potential tends rapidly to zero. Consequently, the wavefunctions presented in this article are expected to be trustworthy at distances of a couple of Angstrom from the surface S_1 .

4.1 Eigenfunctions and eigenenergies

We studied only the case that the C oulom b potential $Z \notin = (r"_I)$ within the insulator (R_2 r R_1) is small compared to the barrier height B which is related to the gap parameter B_0 by Eq. (4). This means that we neglected the C oulom b potential in region I.

Table 1: The energies $Ze_0^2 = (R_2 "_I)$, $Ze_0^2 ("_I = 1) = (R_1 "_I)$, and the barrier height B as a function of the radii R_1 and R_2 and of the dielectric constant "_I. Energies are given in meV and radii in A. The parameter B_0 is chosen equal to 2500 meV or 4000 meV.

R ₂ (A)	20	20	20	10	10	10	3.5	3.5
R ₁ (A)	28	28	28	18	18	18	10	10
"I	115	28	10	115	28	10	115	10
	(T iO ₂)	(Hg0)	(A 1203)	(T iO ₂)	(Hg0)	(A 1203)	(T iO ₂)	(A l ₂ 0 ₃)
Z	1	1	1	1	1	1	1	1
$\frac{Z e_0^2}{R_2 "_I}$ (m eV)	626	25.7	72	12.5	51.4	144	35.8	411
$\frac{Z e_0^2 ("_I 1)}{R_1 "_I}$ (m eV)	509.8	495.9	462.9	793	771	720	1427	1296
B (m eV) for $B_0 = 4000$	3490	3504	3537	3207	3229	3280	2573	2704
B (m eV) for $B_0 = 2500$	1990	2004	2037	1707	1729	1780	1073	1204

In Table 1 we present the energies $Ze_0^2 = (R_2 "_I), Ze_0^2 ("_I = 1) = (R_1 "_I)$, and the barrier height B for typical values of the parameters $R_{1,2}$ and "_I. It is seen that neglecting the screened C oulom b potential $Ze_0^2 = (R_1 "_I)$ in region I as compared to B is sometimes a very good approximation, but, not in general, especially not for Z > 1 and for radii $R_{1,2} = 10A$.

The eigenvalues were determ ined by a num erical solution of the eigenvalue equation (69) using the form of $d \ln R_{I}(R_{1})=dR_{1}$ as given by the Eq. (71), (65), and (66). Up to the common norm alization factor N (see (52)), the radial eigenfunctions R (r; l; E) are then obtained from the equations (11), (18), and (20) in the regions II, I, and 0, resp.

In order to simplify the comparison of results which correspond to di erent choices of the parameters $R_{1,2}$, B, V_{II} and Z, it is advantageous to use the energy unit $Z e_0^2 = R_1$, i.e. the value of the C oulom b potential at the outer surface S_1 . The resulting dimensionless quantities are denoted by

$$" \coloneqq \frac{E}{Z e_0^2 = R_1} ; \qquad (152)$$

$$b \coloneqq \frac{B}{Z e_0^2 = R_1};$$
(153)

$$\mathbf{v}_{\Pi} \coloneqq \frac{\mathbf{V}_{\Pi}}{\mathbf{Z} \, \mathbf{e}_0^2 = \mathbf{R}_1} \, ; \tag{154}$$

$$\mathbf{"}_{m ax} \coloneqq \frac{(V_{\Pi} + Z e_0^2 = R_2)}{Z e_0^2 = R_1} = \frac{E_{m ax}}{Z e_0^2 = R_1} = v_{\Pi} + \frac{R_1}{R_2} :$$
(155)

Furtherm ore, it is convenient to introduce the typical length parameters R_0 and $R_{00} = 0,264589 A$:

$$R_0 = \frac{h^2}{2M e_0^2 Z} - \frac{R_{00}}{Z}$$
 (156)

It what follows we give some technical details concerning the determ ination of the eigenvalues and eigenenergies.

In region I, due to our approximation, the radial eigenfunction R_{I} is given by Eq. (18), i.e. as a linear superposition of the modi ed spherical Bessel functions $f_{1}^{(1)}(x)$ and $f_{1}^{(2)}(x)$ de ned in (53) and (54) with x Ir. We calculate these functions by representing them in the form (see Ref. [5], Chapt. 10)

$$f_{1}^{(1)}(x) = \frac{1}{2x} R l + \frac{1}{2}; x e^{x} + (1)^{l}R l + \frac{1}{2}; x e^{x};$$
 (157)

$$f^{(2)}(x) = \frac{1}{2x}R + \frac{1}{2};x e^{-x}$$
 (158)

as a linear superposition of exponentially rising and decreasing terms. Here, the function R $1+\frac{1}{2}$; x is de ned (see Ref. [5], Eq. (10.2.11)) as

$$R \quad l + \frac{1}{2}; x := \sum_{k=0}^{X^{l}} l + \frac{1}{2}; k \quad (2x)^{k}; \qquad (159)$$
$$l + \frac{1}{2}; k := \frac{(l+k)!}{k!(l-k)!}:$$

It turned out to be convenient to rewrite $R_{I}(r)$ in the form

$$R_{I}(\mathbf{r}) = A_{I}^{0}g_{I}^{(1)}(\mathbf{x})e^{\mathbf{x}} {}^{IR_{2}} + \frac{1}{-}^{h}B_{I}^{0} + (1)^{l}A_{I}^{0}e^{2_{II}R_{2}}^{i}$$

$$\overset{(2)}{\mathcal{G}}(\mathbf{x})e^{-(\mathbf{x}} {}^{IR_{2}}); \qquad (160)$$

where the functions $g_{1}^{(1;2)}\left(x\right)$ are related to $f_{1}^{(1;2)}\left(x\right)$ by

$$g_1^{(1)}(x) \coloneqq f_1^{(1)}(x) e^{-x};$$
 (161)

$$g_1^{(2)}(x) \coloneqq f_1^{(2)}(x)e^x$$
: (162)

The amplitudes A_{I}^{0} , B_{I}^{0} are connected with the amplitudes A_{I} and B_{I} of Eq. (18) by

$$A_{I}^{0} = A_{I} e^{I^{R_{2}}}$$
; (163)

$$B_{I}^{0} = [(1)^{l+1}A_{I} + B_{I}]e^{-IR_{2}} :$$
 (164)

The advantage of using (160) instead of (18) is that the functions $g_1^{1,2}$ (y) can be num erically determ ined m ore com fortably than the functions $f_1^{(1,2)}$ (y) and that they have a simpler asymptotic behaviour

$$g_{1}^{(1)}(\mathbf{x}) ! \frac{1}{2\mathbf{x}} + 0 \frac{1}{\mathbf{x}^{2}}$$
; (165)

$$g_1^{(2)}(x) ! \frac{1}{2x} + 0 \frac{1}{x^2}$$
 : (166)

From the continuity conditions (46), (47) one obtains A_{I}^{0} and B_{I}^{0} in the form

$$A_{I}^{0} = \frac{2}{-} ({}_{I}R_{2})^{2} dg_{1}^{(2)} ({}_{I}R_{2}) {}_{1}\mathbf{j}_{II}R_{2} - \frac{\pi}{-} g_{1}^{(2)} ({}_{I}R_{2})\mathbf{j}_{1}^{0} ({}_{II}R_{2}) ; \qquad (167)$$

$$B_{I}^{0} = (1)^{l+1}A_{I}^{0}e^{-2} {}_{I}R_{2} + 2({}_{I}R_{2})^{2} dg^{(1)} ({}_{I}R_{2})\mathbf{j}_{1} ({}_{II}R_{2})$$

$$\frac{\Pi}{I}g_{1}^{(1)}(I_{R}R_{2})j_{1}^{0}(I_{R}R_{2}); \qquad (168)$$

where the function $dg^{(1;2)}(x)$ are dened by

$$dg^{(1)}(\mathbf{x}) = e^{-\mathbf{x}} f_{1}^{(1)^{0}}(\mathbf{x}) ; \qquad (169)$$

$$dg^{(2)}(x) = e^{+x} f_{1}^{(2)}(x) :$$
 (170)

Then, the continuity condition (69) assumes the explicit form

$$F (") := U + 1 \frac{d_0}{2}; 2l + 2; 2 R_1 [R_1 + R_1 R_1] + 2 R_1 (l + 1 \frac{d_0}{2}) U + 2 \frac{d_0}{2}; 2l + 3; 2 R_1 R (171) + (R_1) U + 1 \frac{d_0}{2}; 2l + 2; 2 R_1 R = 0$$

with

$$R_{I} \coloneqq R_{I}(R_{1}) ; \qquad (172)$$

$$\mathbf{\tilde{R}}_{I} := \mathbf{A}_{I}^{0} \mathbf{g}_{l+1}^{(1)} (_{I} \mathbf{R}_{1}) \mathbf{e}^{_{I}(\mathbf{R}_{1} - \mathbf{R}_{2})} - \frac{1}{-} \mathbf{B}_{I}^{0} \mathbf{g}_{l+1}^{(2)} (_{I} \mathbf{R}_{1}) \mathbf{e}^{_{I}(\mathbf{R}_{1} - \mathbf{R}_{2})} \\ - \frac{(-1)^{l+1}}{-} \mathbf{A}_{I}^{0} \mathbf{g}_{l+1}^{(2)} (_{I} \mathbf{R}_{1}) \mathbf{e}^{_{I}(\mathbf{R}_{1} - \mathbf{R}_{2})} \mathbf{e}^{_{2}_{I} \mathbf{R}_{2}} :$$
(173)

In terms of the dimensionless parameters (152) to (155) the arguments which appear in the transcendental equation (171) take the form

$$_{I}R_{1} = \int_{S}^{S} \frac{\overline{R_{1}}}{R_{0}}^{q} \frac{1}{b+j'} j; \qquad (174)$$

$${}_{\mathrm{II}}\mathbf{R}_{2} = \underbrace{\frac{\mathbf{R}_{2}}{\mathbf{R}_{0}}}_{\mathrm{s}} \frac{\mathbf{R}_{2}}{\mathbf{R}_{1}}^{\mathrm{q}} \frac{\mathbf{R}_{2}}{\mathbf{b} + \mathbf{j}^{\mathrm{r}}} \mathbf{j} = \underbrace{\frac{\mathbf{R}_{2}}{\mathbf{R}_{0}}}_{\mathrm{s}} \frac{\mathbf{R}_{2}}{\mathbf{R}_{1}}^{\mathrm{q}} \frac{\mathbf{R}_{2}}{\mathbf{R}_{1}}^{\mathrm{q}} \mathbf{j}; \qquad (175)$$

$$R_1 = \frac{R_1 p}{R_0} \overline{r}; \qquad (176)$$

$$d_{0} = \frac{R_{1}}{R_{0}} \frac{1}{p_{\pi}} :$$
 (177)

We determ ined the zeros of the function F (") by calculating numerically F (") in small steps of " between limits " $_{m in}$ and " $_{m ax}$. Whenever F (") changed sign from a given step to the next one, we rened the mesh by usually a factor of 100 so as to determ ine the zero with the desired accuracy. We note that, for each given value of the angular momentum 1, there is an in nity of eigenvalues as " approaches " = 0 from below. This is so as a result of the in nite range of the C oulom b potential in region 0. In the domain of small j" j i.e. of very weakly bound electrons, and also for large well depth v_{II} , the function F (") oscillates between large positive and negative values. Nevertheless, for a su ciently narrow system of mesh points, the function F (") is of reasonable size for the meshpoint closest to a zero. Therefore, we encountered no problem s of numerical accuracy in determ ining the eigenvalues.

Once an eigenvalue is determined, the amplitudes A_{I}^{0} , B_{I}^{0} are obtained from (167), (168) then A_{I} , B_{I} from (163), (164). The amplitude C_{0} of the radial wavefunction R_{0} (r) in region 0 (see Eq. (34) is found from the continuity condition (48) and, nally, the overall norm alisation constant N from (52). The integral in Eq. (52) is done num erically.

We note that the numerical determination of the eigenvalues and eigenfunctions turned out to be extremely rapid. Thus it is conceivable that one uses these eigenfunctions (in principle completed by the scattering states) as basis functions for diagonalizing the additional polarization potentials studied in Sec. 3. We note in passing that A_{I}^{0} has in general a very small value which is dicult to obtain with su cient accuracy from Eq. (167). It turned out that an accurate value of A_{I}^{0} can be obtained by solving the equation (171) for A_{I}^{0} at the value of the eigenvalue which had been determined before.

It is found that there are 3 classes of eigenfunctions: "external" or "class 1"-states which are predom inantly localized in the vacuum outside of the insulator $(r > R_1)$, "internal" or "class 2"-states which are mainly localized within the metallic core $(r < R_2)$, and "class 3"-states which exhibit a non-negligible probability amplitude both in region 0 and region II. For a su ciently large value of B, the probability for noting the electron in region I, i.e. within the insulator, turns out to be negligibly small. The spectrum of class 1-states resembles the C oulomb spectrum. On the other hand, the eigenvalues of class 2-states, in low est approxim ation, are given by the eigenvalues of an in nite spherical square well of radius R_2 i.e. by the boundary condition $j_1(_{II}R_2) = 0$.

If $_{II}R_2$ 1, the spherical Bessel function $j_1(_{II}R_2)$ can be approximated by

$$j_{\rm L}(_{\rm II}R_2) = \frac{1}{_{\rm II}R_2} \cos_{\rm II}R_2 = \frac{1}{2} - \frac{1}{4}$$
 (178)

The zeros of this function together with (12) lead to the energy form ula

$$E_{nl} = = V_{II} - \frac{Z e_0^2}{R_2} + \frac{h^2}{2M R_2^2} - \frac{3}{4} + n + \frac{1}{2} + \frac{1}{2}; \qquad (179)$$

where n = 0;1;:::as well as l.

The spacing between neighbouring levels of given lor given n is

$$E_{n+1;1}$$
 $E_{n1} = \frac{h^2}{2M} \frac{2}{R_2^2} \frac{5}{2} + 2n + 21$; (180)

$$E_{n;l+1} = \frac{h^2}{2M R_2^2} + n + \frac{1}{2}$$
 (181)

One should notice the completely di erent spacing of the eigenvalues of internally located electrons from the Coulomb dominated spacing of externally located electrons. Of course, if $_{\rm IIR_2}$ is not large compared to 1, the simple results (178) to (181) do not hold.

If it happens that, for given 1, the energy of a predom inantly externally and of a predom inantly internally localized state come very close to each other, the corresponding eigenfunctions are not negligible in both the regions II and 0. We call eigenstates of this nature "class 3"-states. These states play an important role in the lifetime of the system and we shall come back to them in Subsec. 4.2.

In Fig. 3, we show the spectrum of eigenvalues " for l = 0, l = 1, and l = 10 for a given set of parameters. We note that, apart from the dimensionless parameters de ned in the text, lengths are given in Angstrom (10⁻¹⁰ m) and energies in meV (10⁻³ eV).

Given the energy unit $Ze_0^2=R_1 = 514 \text{ m eV}$ in Fig. 3, the **j** jvalues belonging to externally located states must be smaller than 514 m eV. The lowest-lying external state corresponds to the lowest line of the bunch of narrow ly spaced lines at the top of the spectrum at " = 0;68 or E = 350 m eV. Note that the energy di erence between the rst excited external s-state and the lowest external s-state is about 69,5 m eV. This is also the order of magnitude of the average distance between low-lying external levels. Since the "room tem perature" of 300 K

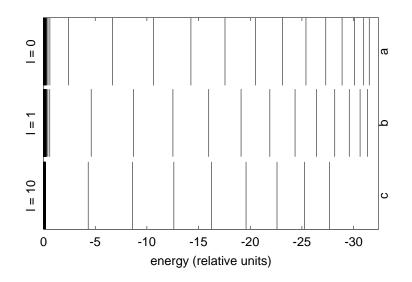


Figure 3: Comparison of the spectra of l = 0 states (Fig. 3a) and l = 1 states (Fig. 3b) and l = 10 states (Fig. 3a) for the following set of parameters: Z = 1, $R_1 = 28$ A; $R_2 = 20$ A; $V_{II} = 15950$ meV; b = 5:83; $v_{II} = 31:031$, $R_0 = 0:271$ A; "min = 0:1; "max = 32:41; energy mesh " = 0:0001. Energy unit: $Z e_0^2 = R_1 = 514$ meV.

corresponds to 26 m eV, one m ay conclude that, at room tem perature, for the parameter set chosen in Fig. 3, the externally bound electrons are predom inantly in their lowest available states.

The spectrum of eigenvalues boks similarly for dimensional values of the angularmomentum 1. The fact that we show only the subsets of eigenvalues for given 1-values in Fig. 3 should not lead to the enroneous in pression that the levels of internally located electrons are so widely spaced that in general, no level of internal electrons is to be expected in the range of energies of external electrons. This is not so due to the fact that there are also the levels for $1 \leq 0$. Consequently, there are generally "intruders" of internal levels in the spectrum of external ones and, consequently, there is in general also a limited number of "class 3-states" which. as we shall show, lead to rapid decay.

We should also notice in Fig. 3 that the distance between successive eigenvalues for given 1 increases with increasing eigenvalue, i.e. as J'j! 0. The reason for this trend is qualitatively seen from the formulae (180) and (181). For the parameter set chosen in Fig. 3, these approximate formulae are only valid for the high-lying levels.

In Fig. 4, we show the wavefunctions corresponding to internal s-states with 0, 1, and 8 radial nodes. It should be noted that even for the case of the highest one with 8 radial nodes at j'j = 17;96, the localization within region II is perfect and the tails in region I are very tiny.

In Fig. 5, we present a comparison of external s-wavefunctions for radial node numbers n = 0;1, and 5. Again one notices that the wavefunctions dive only weakly into region I and are completely negligible in region II. The energy di erence (E $_{n=1;l=0}$ E $_{n=0;l=0}$) between the two lowest-lying external levels turns out to be 96 m eV. The parameter set was chosen to be the same for the Figs. 3{5.

For the high-lying eigenenergy $E_{n=8;l=0}$ 93;5 meV the most external maximum of the wave function is seen to occur at r 130A whereas the wavefunction of the lowest external s-state with n = 0 becomes vanishingly small already at r 60A. This strong dependence of

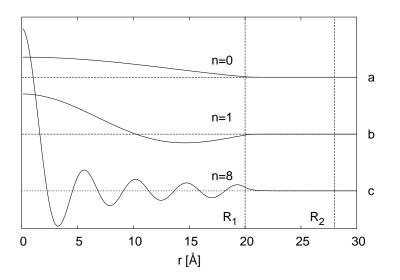


Figure 4: Internally located wavefunction (class 2-states) with radial node number n = 0 (Fig. 4a), n = 1 (Fig. 4b), and n = 8 (Fig. 4c). Orbital angular momentum l = 0. Energies (in units of $Z e_0^2 = R_1 = 514$:3 meV): j" (n = 0; l = 0) j = 32; 235; j" (n = 1; l = 0) j = 31; 698; j" (n = 8; l = 0) j = 17:963. Choice of parameters as in Fig. 3.

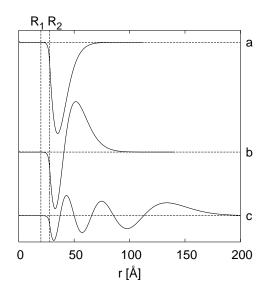


Figure 5: Externally located wavefunctions (class 1-states) with radial node number n = 0 (Fig. 5a), n = 1 (Fig. 5b) and n = 5 (Fig. 5c). Orbital angular momentum l = 0 energies (in units of $Z e_0^2 = R_1 = 514$:3 meV): j" (n = 0; l = 0) j = 0:63325; j" (n = 1; l = 0) j = 0:44533; j" (n = 5; l = 0) j = 0:18213. Choice of parameters as in Fig. 3.

the radial extension on the energy of the state is typical for a C oulom b-spectrum .

The class 1- and class 2-states are thus of very di erent nature. The eigenvalues of class 1-states must be above the potential energy ($Z \notin R_1$) on the surface S_1 of the insulator. Their spacing is much smaller than the one of class 2-states and tends to zero as the binding energy approaches zero. The lowering of the well-depth V_{II}^0 by the potential produced by the positive surface charge on the metal surface S_2 and the screening elects in the insulator is given by $[Z \notin = (\mathbf{T}_{IR_2}) + Z e_0^2 (\mathbf{T}_{I} \quad 1) = (\mathbf{T}_{IR_1})]$. This lowering of the Ferm integrate E_F in the metal is larger than the minimal binding energy $[Z \notin R_1]$ of the lowest external electron by the amount

$$E := \frac{Z e_0^2}{"_{I}} \frac{1}{R_2} + \frac{"_{I}}{R_1} + \frac{Z e_0^2}{R_1} = \frac{Z e_0^2}{"_{I}} \frac{1}{R_2} \frac{1}{R_1}$$
(182)

For the choice $R_1 = 28 A$ and $R_2 = 20 A$ and the charge number Z = 1, we have

$$E = \frac{205;7 \text{ m eV}}{"_{I}}$$

ie. a num berbetween {20 and {200 m eV depending on the dielectric constant "I of the insulator.

If there are unoccupied levels between the Fermi energy E_F and $(E_F + j E)$, an electron in the lowest external state can decay into a lower-lying internal state.

4.2 Electrom agnetic decay of external states

For the sake of simplicity, let us consider a system with one external electron and Z positive surplus charges. If the external electron is in some arbitrary externally located state it will rst decay to the lowest-lying external state by a cascade of unhindered transitions. This lowest-lying external state is characterized by the angular momentum l = 0 and has no radial nodes (n = 0).

Subsequently, this lowest class 1-state will decay into lower-lying unoccupied internally located states (class 2-states). The strongest transitions are of multipolarity E1 and we only consider such dipole transitions. Even these most rapid transitions between a class 1 and a class 2 state are reduced in comparison with transitions between states of the same class due to the small overlap between externally and internally located wavefunctions.

The probability per time-unit for a dipole transition from the initial state $_i$ to the nal state $_f$ is given by [8]

$$W_{12} = \frac{4 c}{3} \frac{JE_1}{(hc)^3} JE_1 JE_2 J^2 J^2; \qquad (183)$$

where E_2 and E_1 denote the naland initial energy, resp., and $e_0^2 = (hc)$ is the ne structure constant.

The initial and nalwavefunctions are

$$(r; \#; ') = \Re_{L} (r; E_1) Y_{lm_1} (\#; ');$$
(184)

$${}_{2}(\mathbf{r}; \#') = \Re_{l_{2}}(\mathbf{r}; \mathbb{E}_{2}) \Upsilon_{l_{2}m_{2}}(\#; '); \qquad (185)$$

where we have away the spin-functions, and where \tilde{R}_{l_1} , \tilde{R}_{l_2} are the properly norm alized radial functions (51). The matrix-element factorizes

$$h_{2} jr j_{1} i = \int_{0}^{Z^{4}} dr \mathcal{R}_{l_{2}}(r) r^{3} \mathcal{R}_{l_{1}}(r) \quad d Y_{l_{2}m_{2}} e_{r} Y_{l_{1}m_{1}}:$$
(186)

Table 2: The quantities W_z and W_z entering the dipole transition probability (see Eqs. (188), (189)).

		$\frac{1}{4}$ $\frac{1}{2} = 1$
$m_2 = m_1 + 1$	$W = \frac{n}{\frac{(l_1 m_1 1)(l_1 m_1)^2}{(2l_1 + 1)(2l_1 1)}}$	$W = \prod_{l=1\\ l = 1\\ $
$m_2 = m_1$	$W_{z} = \frac{n_{(l_{1} m_{1})(l_{1} + m_{1})}^{1}}{(2l_{1} + 1)(2l_{1} 1)}^{1}$	$W_{z} = \frac{n}{(l_{1} m_{1} + 1)(l_{1} m_{1} + 2)} \frac{l_{1}}{(2l_{1} + 1)(2l_{1} + 3)} \frac{l_{1}}{2}$
$m_2 = m_1 - 1$	$W_{+} = \frac{n}{\frac{(l_{1}+m_{1})(l_{1}+m_{1}+1)}{(2l_{1}+1)(2l_{1}-1)}} \frac{l_{1}}{2}$	$W_{+} = \frac{n_{(\underline{l}_{1} \ \underline{m}_{1} + 1) \ (\underline{l}_{1} \ \underline{m}_{1} + 2)}}{(2 \ \underline{l}_{1} + 1) \ (2 \ \underline{l}_{1} + 3) \ 2} \frac{1}{2}$

It is easily seen that the following relation holds:

^Z d Y_{l₁m₁}
$$\mathbf{e}_{\mathbf{r}}$$
Y_{l₂m₂}² = \mathbf{j} W₊ \mathbf{j} + \mathbf{j} W₂ \mathbf{j} + \mathbf{j} W₂ \mathbf{j} ; (187)

where the quantities W and W_z are dened by

$$W := \frac{\int_{a}^{b} \frac{1}{2} dY_{l_{1}m_{1}}Y_{1; 1}Y_{l_{2}m_{2}}; \qquad (188)$$

$$W_{z} := \frac{4}{3}^{2} dY_{l_{1}m_{1}}Y_{10}Y_{l_{2}m_{2}}$$
: (189)

They are evaluated in terms of C lebsch-G ordan coe cients using the W igner-E dkart theorem [9]:

$$W \coloneqq \sum_{s=1}^{s} \frac{\overline{2l_{2}+1}}{2l_{1}+1} C (l_{2}1l_{1};m_{2}; 1;m_{1})C (l_{2}1l_{1}000); \qquad (190)$$

$$W_{z} \coloneqq \frac{2l_{2}+1}{2l_{1}+1}C (l_{2}l_{1}m_{2}Om_{1})C (l_{2}l_{1}OOO) :$$
(191)

The non-vanishing values for W and W_z are presented in Table 2. The radial integral, i.e. the 1^{st} factor in Eq. (186) is evaluated num erically.

We consider the case that the initial state is the lowest external state, i.e. a nodeless wavefunction with $l_1 = 0$. Thus, the nalangularmomentum l_2 is equal to 1.

The nalm agnetic m om ents m₂ m ay have the value m₂ = 1;0;+1.

We are mainly interested in the lifetime fa = 0 of a "mesoscopic atom" which is the inverse of the total decay rate P:

$$= \frac{1}{P} :$$
 (192)

The total decay rate P is defined by summing the transition probabilities W_{12} over all the unoccupied nal states $_2$ which are connected with the initial state $_1$ by a nite matrix element h_1 jrj $_2$ i:

$$P = \int_{2}^{X} W_{12} :$$
 (193)

Considering only dipole transitions is, of course, an approximation which yields only a lower lim it for the total transition rate and an upper lim it for the lifetime.

The restriction of the sum in (193) to unoccupied internal electronic states is indicated by the prime '.

Table 3: Separation energy W $_0$ of an electron, Ferm i-energy E $_F^0$ and well depth V_{II}^0 of uncharged m etals (in meV).

	Be	Na	Al	Ca	Fe	Сs	Au
W ₀	3920	2350	4250	2800	4310	1810	4300
E _F ⁰	14300	3240	11700	4690	11100	1590	5530
V _{II}	18220	5590	15950	7490	15410	3400	9830

Table 4: Lifetime as a function of the outer radius R_1 (A) for: Z = 1; $R_2 = 20$ A; B = 3000 m eV; $V_{T}^0 = 15950 \text{ m eV}$ (A.). Lifetimes in units: sec, minute (min), day (d), year (a).

	<u></u>	· /			,	•	,, 1	()]]
R_1	26	28	30	32	34	36	38	40
	4.83 sec	52 . 9 sec	20.4 m in	9 . 76 h	12 . 9 d	432 d	40 . 8 a	1431 a

At temperature 0, a dipole transition starting from the initial external s-state can go into all the $l_2 = 1$ states the energy of which is between the Ferm i energy E_F^0 and the energy E_1 of the initial state

$$E_{F}^{0} < E_{2} < E_{1}$$
:

At nite tem perature, one has to weigh all the nal states with the factor

$${}^{2}_{41} \quad \frac{1}{\exp \frac{E_{2}}{T} + 1} {}^{5} :$$

So far, we calculated the lifetime for the case T = 0 only.

In Table 3, we present the well depth V_{II}^0 , the separation energy W_0 , and the Ferm i energy $E_F^0 = V_{II}^0$ W_0 for a couple of m etals. We note that these empirical parameters have been determ ined for materials with macroscopic size, not for mesoscopic clusters of such materials. Nevertheless, the parameters can be expected to be essentially correct also for mesoscopic system s.

Let us now come to the results we obtained for the lifetime as a function of the dimensional parameters of the system. We studied separately the dependence of the lifetime on the parameters R_1 , B, Z, and R_2 , keeping always all but one parameter xed.

D ependence of on R_1

A ugm enting R_1 for xed value of R_2 enlarges the width of the barrier and, consequently, decreases the amplitude which an externally located electron has in the inner region II. As the decay of a class 1-state into a class-2 state depends strongly on this tail, the transition probability must decrease and the lifetime must increase as a function of rising R_1 . The results presented in Table 4 support this expectation. The lifetime is found to rise roughly exponentially with ($R_1 = R_2$). This is so because the amplitude of the tail in region II depends exponentially on ($R_1 = R_2$) as one can see from W KB. The dependence of on R_1 is also shown in Fig. 6 in logarithm ic scale.

Dependence of on the barrier height B

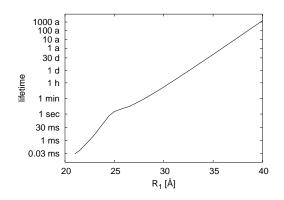


Figure 6: Lifetime in sec and logarithm ic scale as a function of radius R_1 . A part from R_1 , all the other parameters are chosen as in Fig. 3.

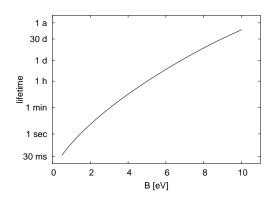


Figure 7: Lifetime in sec and logarithm ic scale as a function of the barrier height B. A part from B, all the other parameters are chosen as in Fig. 3.

In Fig. 7, we show the dependence of the lifetime on the barrier height B in logarithm ic scale. The lifetime increases as a function of rising B. The increase is somewhat smaller than exponential as can be expected from WKB.

D ependence of on R_2 and on Z

If one changes R_2 with all the other parameters xed, one modiles predominantly the internally located class 2 states and the corresponding energies. As one can see from Fig. 8, the lifetime as a function of rising R_2 decreases on the average as one would expect from the fact that the thickness ($R_1 = R_2$) of the surface layer decreases. However, beside the average decrease of the lifetime, one observes a kind of resonance structure: W ithin a change of R_2 by 1 A, the lifetime can change by 10 orders of magnitude.

How can we understand these huge uctuations of the lifetime?

In Fig. 9, we show the probability of an externally located electron to be found in the inner region II. This localization probability in region II, which is of crucial importance for the transition rate, is seen to show pronounced peaks at precisely those values of R_2 , where the lifetime has very small values as one can see by comparing Fig. 8 and Fig. 9. The large variations of the transition rate as a function of R_2 (and of Z) can be simply explained as follow s:

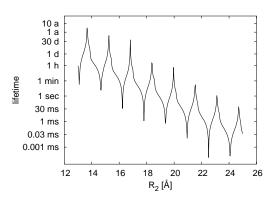


Figure 8: Lifetime in sec and logarithm ic scale as a function of R_2 . Apart from R_2 , all the other parameters are chosen as in Fig. 3.

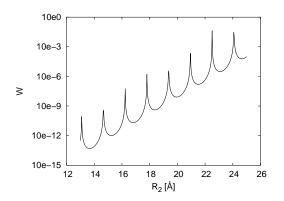


Figure 9: Probability (W) of lowest external electron to be found in the inner region II (R < R₂) as a function of R₂. Apart from R₂, all the other parameters are chosen as in Fig. 3.

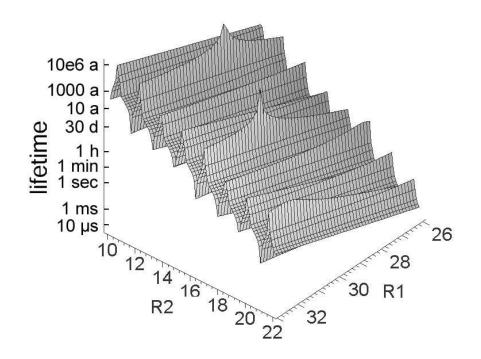


Figure 10: Lifetime (sec, log.scale) as a function of radius R_1 and R_2 (in A) in a 3-dimensional plot. Except for R_1 and R_2 , all the parameters are chosen as in Fig. 3.

As one changes R₂ (or Z), the eigenvalues of class 2-states move whereas the ones of class 1-states remain essentially the same. More specially, the eigenvalues $E_{n1} =$ \mathbf{E}_{n1} jof class-2 states are low ered, if the inner radius R₂ or the positive surplus charge Z is increased. Thereby, it happens regularly that a class 2-state which has the same angular momentum 1 as the decaying class 1-state, crosses the energy of this class 1-state. If one augments R_2 or Z on a su ciently long scale, such crossings occur several times. C lose to the crossing, the external class 1-state develops a non-negligible amplitude within region II and the class 2-state develops an appreciable am plitude in the external region 0. We call such mixed states "class 3-states". If the decaying class 1-state happens to have the nature of a class 3-state, its decay probability to lower-lying class 2-states is considerably enhanced as compared to the ordinary situation where no class 2-state of the same angular momentum is available. We note in passing that this enhancem ent of the transition probability to low er-lying class 2-states does not only occur for dipole transitions but also for transitions of higher multipolarity. So far we have not yet calculated the transition rates of higher multipolarity, because they would only matter if the decaying external state is a class 3-state.

The phenom enon can be considered as an example of the mechanism which Landau and Zener had studied in famous papers [10]. This is demonstrated in Appendix.

In Fig. 10, the dependence of the lifetime on the radii R_1 and R_2 is shown in a 3dimensional plot. A gain one notices that the dependence of on R_1 is smooth whereas the one on R_2 contains "resonances".

In Fig. 11, the energy di erence between the lowest-lying class 1 state and the closest lying class 2-state of the same angular momentum is shown. The plot supports the explanation of

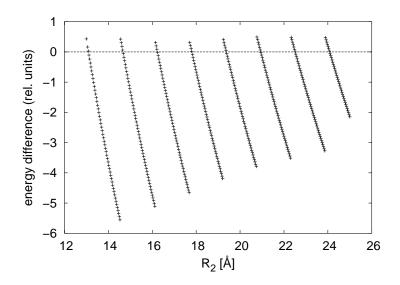


Figure 11: Energy di erence between lowest-lying class 1-state and the closest lying class 2state of the same angular momentum as a function of R_2 (A). Energies are given in units of $Z e_0^2 = R_1 = 5143$ meV. Except for R_2 , all the other parameters are chosen as in Fig. 3.

the resonance phenom enon in term s of a coupling between close-lying states.

In the num erical results presented in this section, the values B of the barrier in region I and the well depth V_{II} of the average potential in region II and the dielectric constant "I were chosen arbitrarily, and not determ ined for given choices of the material.

5 Summary and Discussion

In this paper, we determ ined the quantum states and eigenenergies of an electron in the average potential produced by a positively charged m etal cluster which is covered by an insulating surface layer. Because of the similarity of the externally localized electronic states with the bound states of an electron in the C oulom b potential of an atom, we occasionally referred to the system as a "m esoscopic atom" or, in case of a non-zero total charge, as a "m esoscopic ion".

In particular, we investigated the electrom agnetic decay of an externally located electron ("class 1-state") to a lower-lying unoccupied electronic state located within the metal ("class 2-state"). It turned out that the life-time depends sensitively on the radius R_2 of the metal core and on the number Z of positive surplus charges of the metal. In the model we studied, we found life-times varying between 10⁻¹⁰ s and years depending on the value of R_2 or of Z.

The value B of the barrier height was $3 \, \text{eV}$ in our calculations. The lifetim e depends strongly on the value of this parameter and decreases for decreasing B .

The origin of the large uctuations was found to be the appearance of states with nonnegligible amplitudes both outside <u>and</u> inside of the insulating surface layer ("class 3-states"). The mechanism leading to these "class 3-states" is described in Appendix.

The wavefunctions and eigenenergies were calculated neglecting the polarization of the insulating surface layer by externally located electrons. The potential produced by these electronic polarization e ects was determined in Sec. 3. It was shown that this additional potential matters mainly in the vicinity of the outer surface S_1 of the insulator and decreases exponentially outside of this surface. The polarization potential could be taken into account by diagonalizing the total H am iltonian including the polarization potential in the basis of the wavefunctions determined in this paper.

A part from this physical simplication of the problem we neglected the C oulom b potential produced by the positive surplus charge within the insulator. This approximation is justified whenever the change of the C oulom b potential within the insulating surface layer is much smaller than the barrier height B_0 . This condition was fullled in all the cases we studied numerically.

Let us now turn to the discussion of som e open questions:

Is the model su ciently realistic?

Certainly, our model should only be regarded as a statep which has to be improved in various respects.

The 1st in provem ent we already mentioned is to incorporate the additional potential between the external electron and the polarization cloud it produces in the insulator. The form of this electronic polarization potential was derived in Sec. 3.

A 2^{nd} in provem ent would be to replace the constant potentials V_{II}^0 in the m etal and $+B_0$ in the insulator by periodic potentials de ned by the crystal structure of these m aterials. Of course, this is m uch m ore complicated and, to our know ledge, it has rarely been done so far for m esoscopic system s. Furtherm ore, the crystal structure in m esoscopic aggregates is in general poorly known.

As a result, the electronic eigenvalues of the total system are expected to exhibit a band structure similarly to a macroscopic solid, the insulating surface layer being characterized by a completely led valence band and an empty conduction band. The empty conduction band in the insulator can be at negative or at positive energy if the energy of the neutral system plus one electron at in nity is put equal to 0. D escribing the average potential in the insulator by a positive barrier $B_0 > 0$ is only meaningful if the conduction band of the insulator is at positive energy.

As a further restrictive condition for our model to be a reasonable 1^{st} approximation there should be no localized traps for an additional electron in the uncharged insulator. This implies that the individual atom s or molecules of the insulator should not have bound states with an additional electron as a monom er [11]. In general, bound states of an electron with a neutral atom or molecule do not exist for atom s or molecules with completely led shells. Therefore, one should use insulators which exhibit this property. P resumably, A $l_2 0_3$ fulls this condition. F inally, we neglected e ects of the electron-phonon coupling altogether. We presume that they tend to reduce the lifetime, but perhaps not drastically.

W hat were the physical motivations of this investigation

As long as one can only produce a limited number of "m esoscopic atoms", one could just investigate experimentally the elects which we studied in the present paper, especially the amusing strong dependence of the lifetime on the radius and the charge of the metallic core. A lthough we would be highly pleased by an experimental scrutiny of our predictions, still more exciting open questions could be asked, if it were possible to produce longlived systems of the kind we presented in this paper, and in large quantities. In this case, one would have access to the study of molecules formed from mesoscopic atoms and to condensed matter consisting of mesoscopic atoms as building blocks. The presence of externally localized electrons would represent a fundam ental di erence from the case of a condensed system of uncharged m esoscopic clusters. On the one hand, one m ay expect that, in a condensed m atter phase of m esoscopic atom s, the weakly bound external electrons would partly dissociate from their m other atom s and m ove freely in the average eld produced by the charged insulated cores. W e would thus sum ise that such a system would be a (good) conductor. On the other hand, the fact that the building blocks of such a condensed m atter carry charge, will have a profound in uence on the equilibrium state of the m aterial. P robably, its density is lower than for uncharged constituents, where the cohesive forces are of van der W aals type and, consequently, of m uch shorter range.

How far are such dreams from reality?

There are evidently two fundam ental obstacles to overcom e, a theoretical one and an experim ental one.

The theoretical problem is the stability of the charged and insulated single system, and the experimental one is the production of a large number (10^{23}) of such systems.

As we learnt from this paper, a mesoscopic system of the kind we investigated can only be stable in a strict sense, if there is no empty internally located electronic state below the energy of the lowest externally located state which is at an energy slightly above $Z \hat{g} = R_1$.

The positive surplus charge $Z e_0$ on the surface S_2 of the metal leads to a decrease of the well-depth V_{II}^0 ! V_{II} as we have shown in Sec. 3:

$$V_{II} = V_{II}^{0} - \frac{Z e_{0}^{2}}{"_{I}} - \frac{1}{R_{2}} + \frac{"_{I}}{R_{1}} = \frac{1}{R_{1}}$$
(194)

If, for the uncharged m etal, the Ferm i level is at the energy $E_F^0 = V_{II}^0$ (with $V_{II}^0, E_F^0 > 0$), it lies at the modi ed energy

$$E_{F}^{0} V_{II} = E_{F}^{0} V_{II}^{0} + \frac{Z e_{0}^{2}}{"_{I}} + \frac{1}{R_{2}} + \frac{"_{I}}{R_{1}}$$
(195)

in the charged m etal.

So the condition for strict stability is that there is no level of an internally located electron between $E_F^0 - V_{II} < 0$ and $Z \notin = R_1$. As the separation energy $W_0 > 0$ of an electron from the uncharged m etal and the Ferm i energy E_F^0 are related to V_{II}^0 by

$$V_{II}^{0} = E_{F}^{0} + W_{0}; \qquad (196)$$

we can state that strict stability is achieved whenever there is no level between the energies

 $fW_0 \quad Z \notin = "_I \quad [I=R+("_I \quad 1)=R_1]g \text{ and } Z \notin = R_1. This means that, metalwith small W_0 is favourable for stability.$

In an ordinary m etal, the separation energy W₀ is of the order of a couple of eV (examples: W₀(Al) = 4;28 eV; W₀(Ag) = 4;26 eV). In the case of a radius R₂ = 20 A of the m etal core, the distance between neighbouring electronic levels is of the order of 100 m eV. This means that in the case we chose for our num erical investigations, there are many unoccupied levels below the energy of the lowest external electron. However, if we consider a system with an inner radius R₂ 4A, the spacing of internally located electron levels of given lapproaches already 1 eV. It is therefore conceivable that one m ight succeed to model a strictly stable , m esoscopic atom ".

A further trick to widen the spectrum of internally localized electrons would be to replace the m etallic sphere with radius R_2 by a m etallic bubble of outer radius R_2 and a thickness of 1 A to 2 A. In this case the levels di ering by the number of radial nodes would have a much larger spacing.

Can such a system be made experimentally?

This is perhaps possible, if one replaces the charged metal layer by a (charged) fullerene C_{60} , which has a radius of about 3,5 A. The separation energy W₀ of an electron from graphite is known to be W₀ = 3;8 eV.W e sum ise that the separation energy from the fullerene is about the same. Of course, it would no longer be justiled to describe free electrons in the fullerene as moving in a simple square well perpendicular to the sphere S_2 . But the spacing of electronic levels is expected to be in the order of eV.

Finally, one is not limited to the spherical geometry. We may also envisage to consider charged nanotubes consisting of a cylindrical surface crystal of C -atom s covered by an insulating surface layer. The charge could in this case be generated by applying an external voltage to the ends of the nanotubes. A s there is a lot of activity spent on nanotubes presently, we hope that one could succeed to produce sm all m acroscopic am ounts of insulated charged nanotubes in a not too far future. O f course, the problem of the stability of externally localized electrons with respect to electrom agnetic decay would be sim ilar for nanotubes as for the case of the system we investigated. So we hope that our investigation stimulates the interest of the experts in the eld of m esoscopic physics.

A cknow ledgem ent:

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Appendix

Landau-Zener M odel for explaining the appearance of class 3-states

Let us consider the sim plied potential

$$\Psi(\mathbf{r}) = V_{\mathrm{II} 0} (\mathbf{R}_{2} \mathbf{r}) + B_{0} (\mathbf{R}_{1} \mathbf{r})_{0} (\mathbf{r} \mathbf{R}_{2}) \frac{Z e_{0}^{2}}{\mathbf{r}}_{0} (\mathbf{r} \mathbf{R}_{1}) :$$
(197)

...

W e decom pose this potential as follows

$$\dot{\Psi}$$
 (r) = $\vec{\nabla}_1$ (r) + $\vec{\nabla}_2$ (r) ; (198)

$$\Psi_1(\mathbf{r}) = {}_0(\mathbf{r} \quad R_1) \quad B \quad \frac{Z \, e_0^2}{r} ;$$
(199)

#

and de ne the two Ham iltonians

$$\hat{H}_{1(2)} := \hat{T} + \hat{\Psi}_{1(2)}(\mathbf{r}) ; \qquad (201)$$

where P is the kinetic energy operator of radial motion

$$\dot{P} = \frac{h^2}{2M} \frac{d^2}{dr^2} + \frac{2}{r}\frac{d}{dr} \frac{1(l+1)}{r^2}$$
 (202)

The eigenstates $'^{(1)}$, $'^{(2)}$ of the Ham iltonians (201)

$$\hat{H}_{1}'^{(1)}(\mathbf{r}) = E^{(1)}'^{(1)};$$
 (203)

$$\hat{H}_{2}'(2)(\mathbf{r}) = E^{(2)}(2)$$
 (204)

form a non-orthogonal set of basis functions.

We consider an eigenstate of the Hamiltonian fi with eigenenergy E

$$\hat{H} := \hat{T} + \hat{\nabla} (r) ;$$
 (205)

$$\mathbf{\hat{H}} = \mathbf{E} \tag{206}$$

for the special case that the angular m om entum l is the same for all the states and that two specic eigenenergies E $^{(1)}$ and E $^{(2)}$ are very close to the energy E in (206).

Then, we may expect that the expansion of in terms of the basis states ' $^{(1)}$ and ' $^{(2)}$ may be limited to the two states with the energies E $^{(1)}$, E $^{(2)}$ very close to E :

$$j i = A j'^{(1)} i + B j'^{(2)} i$$
: (207)

In principle, we would have to sum over all eigenstates $'^{(1)}$ and $'^{(2)}$ on the righthand side of (207), but of all the expansion coe cients A , B only the ones corresponding to the energies E $^{(1)}$, E $^{(2)}$ closest to E are expected to be large and all the others to be much smaller.

Henceforth, we leave away the subscript for simplifying the notation. It is convenient to introduce the dual basis states $^{(1)}$, $^{(2)}$ de ned by the orthogonality conditions

$$h' \sim {}^{(i)} j' {}^{(j)} i = {}_{ij} ;$$
 (208)

where i and j can be 1 or 2. $\sim^{(1)}$ and $\sim^{(2)}$ can be obtained by diagonalizing the inverse of the overlap matrix

$$M^{(ij)} = h'^{(i)} J'^{(j)} i:$$
(209)

.

It is easily seen that the Schrödinger Eq. (206) together with the assumption (207) leads to the two coupled linear equations

.

where the matrix elements are de ned as follows:

$$V_{1,2}^{ij} \coloneqq h^{(i)} V_{1,2} j^{(j)} i:$$
 (211)

Introducing the abbreviations

$$E^{(1)} = E^{(1)} + V_2^{11}$$
; (212)

$$E^{(2)} = E^{(2)} + V_1^{22}$$
 (213)

the solutions E of the eigenvalue equation

$$(\mathbf{E}^{(1)} \quad \mathbf{E}) \, \mathbf{E}^{(2)} \quad \mathbf{E}) \quad \mathbf{Y}^{2} \quad \mathbf{Z}^{24} = 0$$
 (214)

are given by

$$E = \frac{E^{(1)} + E^{(2)}}{2} - \frac{1}{2}^{q} \overline{(E^{(1)} - E^{(2)})^{2} + 4V_{1}^{12}V_{2}^{21}} :$$
(215)

W riting the two states j i in the form

$$j i = A j'^{(1)} i j'^{(2)} i';$$
 (216)

where

$$= \frac{B}{A}; \qquad (217)$$

one obtains from the Eq. (210) and the amplitudes A from the normalisation of j i.

The physically interesting quantities are the probabilities $W_{+}^{(1;2)}$ and $W_{+}^{(1;2)}$ to nd the system described by j i in the substate $\prime^{(1)}$ or $\prime^{(2)}$. These probabilities are given by the mean-values of the projection operators

$$\dot{\mathbb{P}}_{(1;2)} := j'^{(1;2)} ih' \sim^{(1;2)} j:$$
(218)

It is easily seen that the probabilities are given by the following equations

$$W_{+}^{(1)} = h_{+} \mathcal{P}_{(1)} j_{+} i = \frac{1 + M_{+}^{12}}{1 + 2 M_{+}^{12} + M_{+}^{2}} ; \qquad (219)$$

$$W_{+}^{(2)} = h_{+} \not P_{(2)} j_{+} i = \frac{+(++M^{12})}{1+2+M^{12}+\frac{2}{+}};$$
(220)

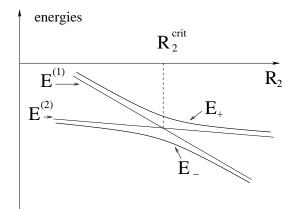


Figure 12: Schematic plot of the Landau-Zener crossing of an external and an internal energy E $^{(1;2)}$ yielding the class 3-state energies E \therefore

$$W^{(1)} = h \quad j^{(1)} j \quad i = \frac{1}{1 \quad 2 \quad M^{12}} ;$$
 (221)

$$W^{(2)} = h \quad j^{(2)}_{(2)} j \quad i = \frac{(M^{12})}{1 \quad 2 \quad M^{12} + 2};$$
 (222)

where M 12 is the overlap of the two basis states

$$M^{12} = h'^{(1)} j'^{(2)} i$$
 (223)

and the quantities by

$$= \frac{1}{2V^{12}} \qquad E^{(1;2)} \qquad \stackrel{q}{\overbrace{(E^{(1;2)})^2 + 4V_1^{12}V_2^{21}}}; \qquad (224)$$

where

$$E := E^{(1)} E^{(2)}$$
: (225)

It is seen that for

$$j E j^2 4 y_1^{12} z^{24} j;$$
 (226)

i.e. far away from the crossing of the energies E $^{(1)}$ and E $^{(2)}$, one of the ratios % (1) is much larger than the other.

For E > 0 one nds

$$= \frac{V_2^{21}}{E}; \qquad (227)$$

$$\frac{E}{V_1^{12}} + \frac{V_2^{21}}{E}^{\#}$$
(228)

and for E < 0 the reversed result

$$+ \frac{E}{V_1^{12}} + \frac{V_2^{21}}{jEj};$$
(229)

$$\frac{V_2^{21}}{jEj}$$
: (230)

This shows that a predom inantly externally localized state turns into a predom inantly internally localized one as the energies E $^{(1)}$ and E $^{(2)}$ cross as a function of R₂ or Z. The coupled true states are thus seen to change their nature as a result of the crossing of the energies E $^{(1)}$, E $^{(2)}$ of a class 1 and a class 2 state. C lose to the crossing point the states are seen to be "delocalized", containing com parable contributions of the two basis states ' $^{(1,2)}$.

This is in essence a Landau-Zener crossing. In Fig. 12 we show a schematic picture of the energies $E^{(1)}$, $E^{(2)}$, E_+ , and E_- as a function of the the parameter R_2 or Z_- .

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